

MOS INTEGRATED CIRCUIT μ PD75P3116

4-BIT SINGLE-CHIP MICROCONTROLLER

The μ PD75P3116 replaces the μ PD753108's internal mask ROM with a one-time PROM, and features expanded ROM capacity.

Because the μ PD75P3116 supports programming by users, it is suitable for use in evaluation of systems in the development stage using the μ PD753104, 753106, or 753108, and for use in small-scale production.

Detailed information about functions is provided in the following User's Manual. Be sure to read it before designing:

 μ PD753108 User's Manual: U10890E

FEATURES

\bigcirc Compatible with μ PD753	108
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O Memory capacity:

PROM: 16384 × 8 bits
 RAM: 512 × 4 bits

 \bigcirc Can be operated in same power supply voltage range as the mask version μ PD753108

• $V_{DD} = 1.8 \text{ to } 5.5 \text{ V}$

On-chip LCD controller/driver

QTOP™ microcontroller

Remark QTOP microcontrollers are microcontrollers with on-chip one-time PROM that are totally supported by NEC Electronics. This support includes writing application programs, marking, screening, and verification.

ORDERING INFORMATION

	Part Number	Package
	μPD75P3116GC-AB8	64-pin plastic QFP (14 × 14)
	μ PD75P3116GK-8A8	64-pin plastic LQFP (12 × 12)
*	μ PD75P3116GC-8BS	64-pin plastic LQFP (14 \times 14)
*	μ PD75P3116GC-8BS-A	64-pin plastic LQFP (14 × 14)

Caution This device does not provide an internal pull-up resistor connection function by means of mask option.

Remark Products with "-A" at the end of the part number are lead-free products.

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Not all products and/or types are available in every country. Please check with an NEC Electronics sales representative for availability and additional information.



FUNCTION OUTLINE

	Item		Function			
Instruction execution time		• 0.67	 0.95, 1.91, 3.81, or 15.3 μs (main system clock: @ 4.19 MHz) 0.67, 1.33, 2.67, or 10.7 μs (main system clock: @ 6.0 MHz) 122 μs (subsystem clock: @ 32.768 kHz) 			
Internal memory PROM			4 × 8 bits			
	RAM	512×	4 bits			
General-purpose registers			manipulation: 8 × 4 banks manipulation: 4 × 4 banks			
I/O ports	CMOS input	8	Internal pull-up resistor connection can be specified by software setting: 7			
	CMOS I/O	20	Internal pull-up resistor connection can be specified by software setting: 12 Shared with segment pins: 8			
	N-ch open-drain I/O	4	13 V withstanding voltage			
	Total	32				
LCD controller/dri	LCD controller/driver		ment number selection: 16/20/24 segments (switchable to CMOS I/O ports in a batch of 4 pins, max. 8 pins) slay mode selection: Static, 1/2 duty (1/2 bias), 1/3 duty (1/2 bias), 1/3 duty (1/3 bias), 1/4 duty (1/3 bias)			
Timers		5 cha	5 channels: • 8-bit timer/event counter: 3 channels (Can be used as 16-bit timer/event counter, carrier generator, and timer with gate) • Basic interval timer/watchdog timer: 1 channel • Watch timer: 1 channel			
Serial interface		• 2-wi	3-wire serial I/O mode ··· MSB/LSB first switchable 2-wire serial I/O mode SBI mode			
Bit sequential buff	fer (BSB)	16 bit	16 bits			
Clock output (PCI	_)	Ф, 52- Ф, 75	Φ, 524, 262, and 65.5 kHz (main system clock: @ 4.19 MHz) Φ, 750, 375, and 93.8 kHz (main system clock: @ 6.0 MHz)			
Buzzer output (BL	JZ)		• 2, 4, and 32 kHz (main system clock: @ 4.19 MHz or subsystem clock: @ 32.768 kHz) • 2.93, 5.86, 46.9 kHz (main system clock: @ 6.0 MHz)			
Vectored interrupt	is		• External: 3 • Internal: 5			
Test inputs			External: 1 Internal: 1			
System clock oscillator			Ceramic/crystal oscillator for main system clock Crystal oscillator for subsystem clock			
Standby function		STOF	P/HALT mode			
Power supply volt	age	V _{DD} =	V _{DD} = 1.8 to 5.5 V			
Package		• 64-p	64-pin plastic QFP (14 × 14) 64-pin plastic LQFP (12 × 12) 64-pin plastic LQFP (14 × 14)			



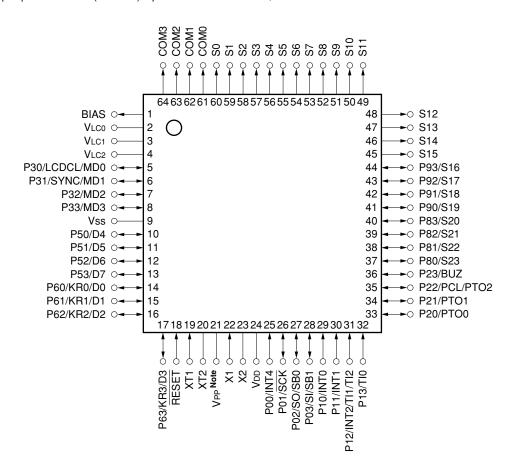
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1. PIN CONFIGURATION (TOP VIEW)

• 64-pin plastic QFP (14 \times 14): μ PD75P3116GC-AB8 • 64-pin plastic LQFP (12 \times 12): μ PD75P3116GK-8A8

 \star • 64-pin plastic LQFP (14 × 14): μ PD75P3116GC-8BS, 75P3116GC-8BS-A



Note Always connect the VPP pin directly to VDD during normal operation.

PIN IDENTIFICATIONS

P00 to P03: Port 0 P10 to P13: Port 1 P20 to P23: Port 2 P30 to P33: Port 3 P50 to P53: Port 5 P60 to P63: Port 6 P80 to P83: Port 8 P90 to P93: Port 9

KR0 to KR3: Key return 0 to 3

SCK: Serial clock
SI: Serial input
SO: Serial output

RESET: Reset

SB0, SB1:

MD0 to MD3: Mode selection 0 to 3 D0 to D7: Data bus 0 to 7

Serial data bus 0, 1

S0 to S23: Segment output 0 to 23

COM0 to COM3: Common output 0 to 3

VLC0 to VLC2: LCD power supply 0 to 2

BIAS: LCD power supply bias control

LCDCL: LCD clock

SYNC: LCD synchronization TI0 to TI2: Timer input 0 to 2

PTO0 to PTO2: Programmable timer output 0 to 2

BUZ: Buzzer clock

PCL: Programmable clock

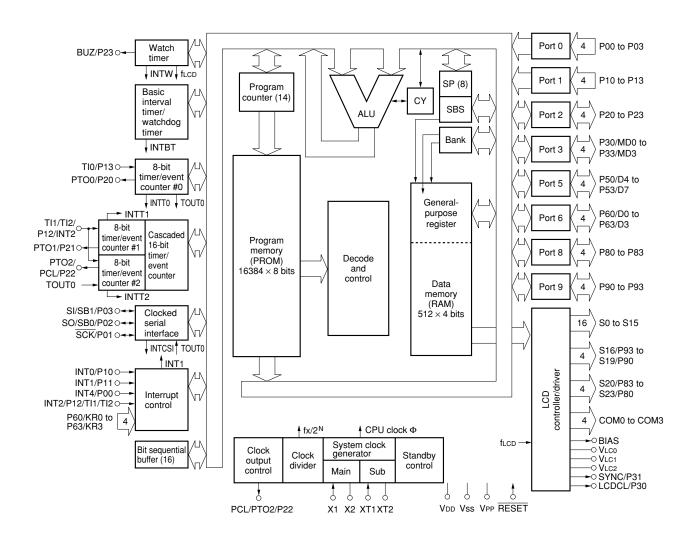
INT0, 1, 4: External vectored interrupt 0, 1, 4

INT2: External test input 2

X1, X2: Main system clock oscillation 1, 2
 XT1, XT2: Subsystem clock oscillation 1, 2
 VPP: Programming power supply
 VDD: Positive power supply

Vss: Ground

2. BLOCK DIAGRAM





3. PIN FUNCTIONS

3.1 Port Pins (1/2)

Pin Name	I/O	Alternate Function	Function	8-Bit I/O	Status After Reset	I/O Circuit Type ^{Note 1}
P00	Input	INT4	4-bit input port (Port 0)		Input	
P01		SCK	Connection of an internal pull-up resistor can be specified by a software setting in 3-bit units.			<f>-A</f>
P02		SO/SB0				<f>-B</f>
P03		SI/SB1				<m>-C</m>
P10	Input	INT0	4-bit input port (Port 1)	_	Input	-C
P11		INT1	Connection of an internal pull-up resistor can be specified by a software setting in 4-bit units. P10/INT0 can be used to select a noise eliminator.			
P12		TI1/TI2/INT2	P 10/INTO can be used to select a noise eliminator.			
P13		TIO				
P20	I/O	PTO0	4-bit I/O port (Port 2)	_	Input	E-B
P21		PTO1	Connection of an internal pull-up resistor can be specified by a software setting in 4-bit units.			
P22		PCL/PTO2				
P23		BUZ				
P30	I/O	LCDCL/MD0	Programmable 4-bit I/O port (Port 3)	_	Input	E-B
P31		SYNC/MD1	Input and output can be specified in 1-bit units. Connection of an internal pull-up resistor can be			
P32		MD2	specified by a software setting in 4-bit units.			
P33		MD3				
P50Note 2	I/O	D4	N-ch open-drain 4-bit I/O port (Port 5)	_	High	M-E
P51 Note 2		D5	When set to open-drain, the withstanding voltage is 13 V.		impedance	
P52Note 2		D6				
P53Note 2		D7				

Notes 1. Circuit types enclosed in angle brackets indicate Schmitt-triggered input.

2. The low-level input leakage current increases when input instructions or bit manipulation instructions are executed.

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3.1 Port Pins (2/2)

Pin Name	I/O	Alternate Function	Function	8-Bit I/O	Status After Reset	I/O Circuit Type ^{Note 1}
P60	I/O	KR0/D0	Programmable 4-bit I/O port (Port 6)	_	Input	<f>-A</f>
P61		KR1/D1	Input and output can be specified in 1-bit units. Connection of an internal pull-up resistor can be			
P62		KR2/D2	specified by a software setting in 4-bit units.			
P63		KR3/D3				
P80	I/O	S23	4-bit I/O port (Port 8)	V	Input	Н
P81		S22	Connection of an internal pull-up resistor can be specified by a software setting in 4-bit units ^{Note 2} .			
P82		S21				
P83		S20				
P90	I/O	S19	Programmable 4-bit I/O port (Port 9)		Input	Н
P91		S18	Connection of an internal pull-up resistor can be specified by a software setting in 4-bit units ^{Note 2} .			
P92		S17				
P93		S16				

Notes 1. Circuit types enclosed in angle brackets indicate Schmitt-triggered input.

^{2.} Do not connect an internal pull-up resistor by software when these pins are used as segment signal outputs.



3.2 Non-Port Pins (1/2)

	I/O	Alternate Function	Function	Status After Reset	I/O Circuit Type ^{Note 1}	
TI0	Input	P13	External event pulse input to timer/ev	Input	-C	
TI1		P12/INT2/TI2				
TI2		P12/INT2/TI1				
PTO0	Output	P20	Timer/event counter output		Input	E-B
PTO1		P21				
PTO2		P22/PCL				
PCL		P22/PTO2	Clock output			
BUZ		P23	Frequency output (for buzzer or systematics)	em clock trimming)		
SCK	I/O	P01	Serial clock I/O		Input	<f>-A</f>
SO/SB0		P02	Serial data output Serial data bus I/O			<f>-B</f>
SI/SB1		P03	Serial data input Serial data bus I/O			<m>-C</m>
INT4	Input	P00		Edge detection vectored interrupt input (valid for detecting both rising and falling edges)		
INT0	Input	P10	Edge detection vectored interrupt input (detection edge is selectable) INTO/P10 can be used to select a	With noise eliminator/ asynchronous is selectable	Input	-C
INT1		P11	noise eliminator.	Asynchronous	-	
INT2	Input	P12/TI1/TI2	Rising edge detection testable input	Asynchronous		
KR0 to KR3	I/O	P60 to P63	Parallel falling edge detection testable	e input	Input	<f>-A</f>
X1	Input	_	Ceramic/crystal resonator connection		_	_
X2	_		clock oscillation. If using an external to X1 and input the inverted signal to			
XT1	Input	_	Crystal resonator connection for subs If using an external clock, input the si	,	_	_
XT2	_		the inverted signal to XT2. XT1 can linput.	be used as a 1-bit (test)		
RESET	Input	_	System reset input (low-level active)		_	
MD0 to MD3	Input	P30 to P33	Mode selection for program memory	(PROM) write/verify	Input	E-B
D0 to D3	I/O	P60/KR0 to P63/KR3	Data bus for program memory (PROI	M) write/verify	Input	<f>-A</f>
D4 to D7		P50 to P53				M-E
VppNote 2	_	_	Programmable power supply voltage memory (PROM) write/verify. During normal operation, connect direction Apply +12.5 V for PROM write/verify.	_	_	
VDD	_		Positive power supply		_	
Vss		_	Ground potential		_	_

Notes 1. Circuit types enclosed in angle brackets indicate Schmitt-triggered input.

2. The VPP pin does not operate correctly when it is not connected to the VDD pin during normal operation.



3.2 Non-Port Pins (2/2)

Pin Name	I/O	Alternate Function	Function	Status After Reset	I/O Circuit Type
S0 to S15	Output	_	Segment signal output	Note 1	G-A
S16 to S19	Output	P93 to P90	Segment signal output	Input	Н
S20 to S23	Output	P83 to P80	Segment signal output		Н
COM0 to COM3	Output	_	Common signal output	Note 1	G-B
VLC0 to VLC2	_	_	Power supply for driving LCD	_	_
BIAS	Output	_	Output for external split resistor cut	Note 2	_
LCDCLNote 3	Output	P30/MD0	Clock output for driving external expansion driver		E-B
SYNCNote 3	Output	P31/MD1	Clock output for synchronization of external expansion driver Input		E-B

Notes 1. V_{LCX} (X = 0, 1, 2) is selected as the input source for the display outputs as shown below.

S0 to S23: VLC1, COM0 to COM2: VLC2, COM3: VLC0

2. When the split resistor is incorporated: Low level

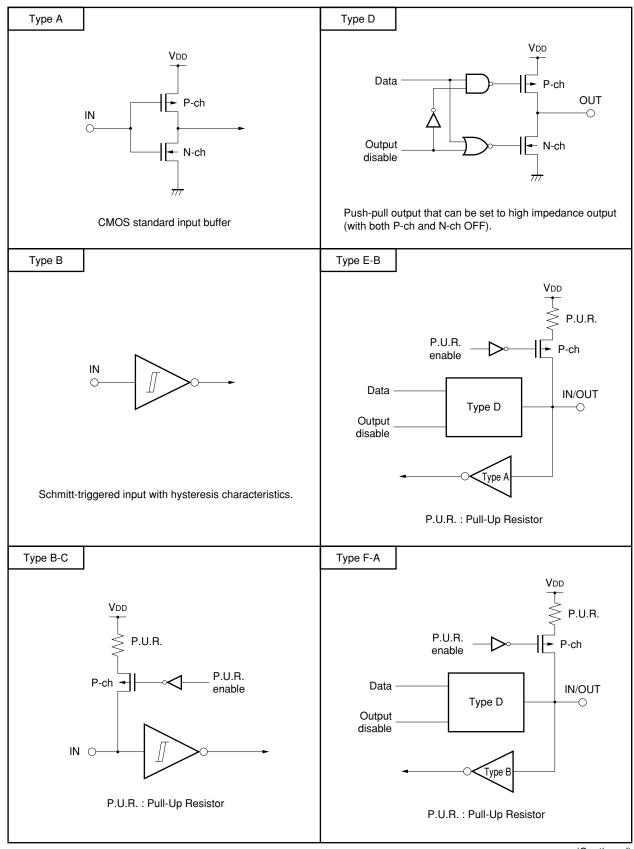
When the split resistor is not incorporated: High impedance

3. These pins are provided for future system expansion. Currently, only P30 and P31 are used.



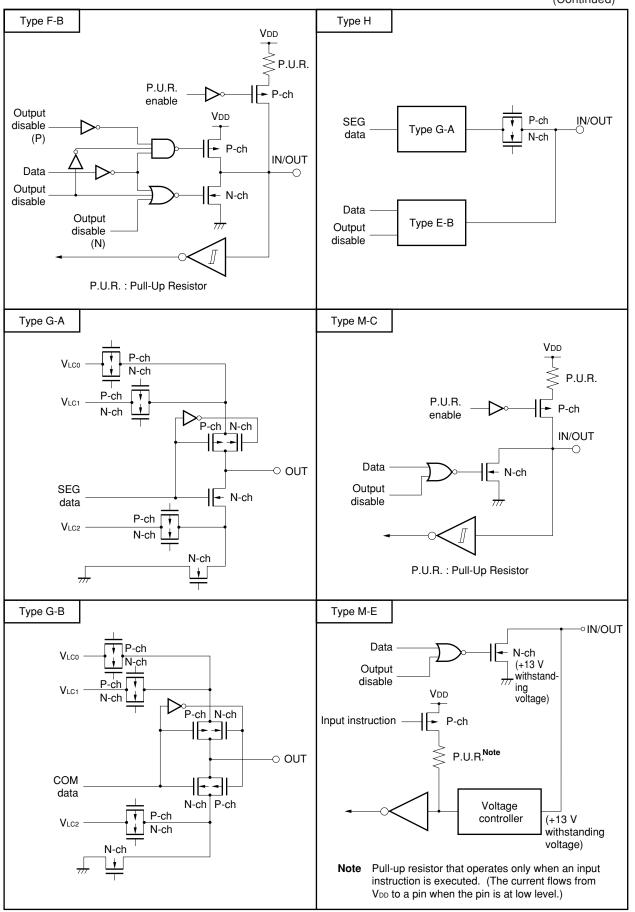
3.3 Pin I/O Circuits

The I/O circuits for the μ PD75P3116's pins are shown in abbreviated form below.



(Continued)

(Continued)





3.4 Recommended Connection of Unused Pins

Table 3-1. List of Unused Pin Connections

Pin	Recommended Connection
P00/INT4	Connect to Vss or VDD.
P01/SCK	Input: Independently connect to Vss or VDD via a resistor.
P02/SO/SB0	Output: Leave open.
P03/SI/SB1	Connect to Vss.
P10/INT0 and P11/INT1	Connect to Vss or VDD.
P12/TI1/TI2/INT2	
P13/TI0	
P20/PTO0	Input: Independently connect to Vss or VDD via a resistor.
P21/PTO1	Output: Leave open.
P22/PTO2/PCL	
P23/BUZ	
P30/LCDCL/MD0	
P31/SYNC/MD1	
P32/MD2	
P33/MD3	
P50/D4 to P53/D7	Input: Connect to Vss. Output: Connect to Vss.
P60/KR0/D0 to P63/KR3/D3	Input: Independently connect to Vss or VDD via a resistor. Output: Leave open.
S0 to S15	Leave open.
COM0 to COM3	
S16/P93 to S19/P90	Input: Independently connect to Vss or VDD via a resistor.
S20/P83 to S23/P80	Output: Leave open.
VLC0 to VLC2	Connect to Vss.
BIAS	Connect to Vss only when none of VLco, VLc1 or VLc2 is used. In other cases, leave open.
XT1 ^{Note}	Connect to Vss.
XT2 ^{Note}	Leave open.
V _{PP}	Always connect to V _{DD} directly.

Note When the subsystem clock is not used, select SOS.0 = 1 (on-chip feedback resistor not used).

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4. Mk I AND Mk II MODE SELECTION FUNCTION

Setting the stack bank selection (SBS) register for the μ PD75P3116 enables the program memory to be switched between the Mk I mode and Mk II mode. This function is applicable when using the μ PD75P3116 to evaluate the μ PD753104, 753106, or 753108.

When bit 3 of SBS is set to 1: Sets the Mk I mode (supports the Mk I mode for the μ PD753104, 753106, and 753108) When bit 3 of SBS is set to 0: Sets the Mk II mode (supports the Mk II mode for the μ PD753104, 753106, and 753108)

4.1 Differences Between Mk I Mode and Mk II Mode

Table 4-1 lists the differences between the Mk I mode and the Mk II mode for the μ PD75P3116.

Table 4-1. Differences Between Mk I Mode and Mk II Mode

Item		Mk I Mode	Mk II Mode		
Program counter		PC13-0			
Program memo	ory (bytes)	16384			
Data memory (bits)	512 × 4			
Stack Stack bank		Selectable via memory banks 0 and 1			
	No. of stack bytes	2 bytes	3 bytes		
Instruction	BRA !addr1 instruction	Not available	Available		
	CALLA !addr1 instruction				
Instruction	CALL !addr instruction	3 machine cycles	4 machine cycles		
execution time CALLF !faddr instruction		2 machine cycles	3 machine cycles		
Supported mask ROM products		When set to Mk I mode: μPD753104, 753106, and 753108	When set to Mk II mode: μPD753104, 753106, and 753108		

Caution The Mk II mode supports a program area exceeding 16 KB for the 75X and 75XL Series. Therefore, this mode is effective for enhancing software compatibility with products that have a program area of more than 16 KB.

With regard to the number of stack bytes during execution of subroutine call instructions, the usable area increases by 1 byte per stack compared to the Mk I mode when the Mk II mode is selected. However, when the CALL !addr and CALLF !faddr instructions are used, the machine cycle becomes longer by 1 machine cycle. Therefore, if more emphasis is placed on RAM use efficiency and processing performance than on software compatibility, the Mk I mode should be used.

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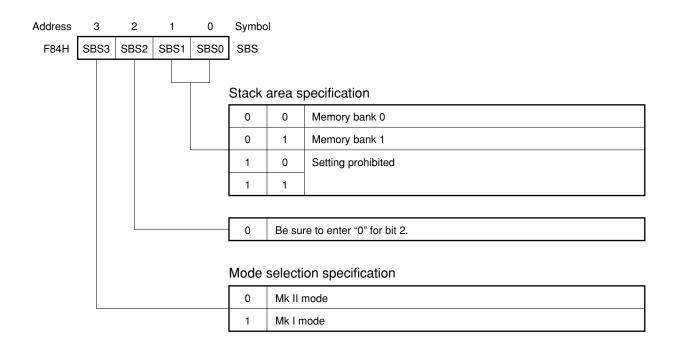
4.2 Setting of Stack Bank Selection (SBS) Register

Use the stack bank selection register to switch between the Mk I mode and Mk II mode. Figure 4-1 shows the format of the stack bank selection register.

The stack bank selection register is set using a 4-bit memory manipulation instruction. When using the Mk I mode, be sure to initialize the stack bank selection register to $100 \times B^{\text{Note}}$ at the beginning of the program. When using the Mk II mode, be sure to initialize it to $000 \times B^{\text{Note}}$.

Note Set the desired value for \times .

Figure 4-1. Format of Stack Bank Selection Register



Caution SBS3 is set to 1 after RESET input, and consequently the CPU operates in the Mk I mode. When using instructions for the Mk II mode, set SBS3 to 0 and set the Mk II mode before using the instructions.



5. DIFFERENCES BETWEEN μ PD75P3116 AND μ PD753104, 753106, 753108

The μ PD75P3116 replaces the internal mask ROM in the μ PD753104, 753106, and 753108 with a one-time PROM and features expanded ROM capacity. The μ PD75P3116's Mk I mode supports the Mk I mode in the μ PD753104, 753106, and 753108 and the μ PD75P3116's Mk II mode supports the Mk II mode in the μ PD753104, 753106.

Table 5-1 lists differences between the μ PD75P3116 and the μ PD753104, 753106, and 753108. Be sure to check the differences between these products before using them with PROMs for debugging or prototype testing of application systems or, later, when using them with a mask ROM for full-scale production.

For details of the CPU functions and internal hardware, refer to the User's Manual.

Table 5-1. Differences Between μ PD75P3116 and μ PD753104, 753106, and 753108

	Item		μPD753106	μPD753108	μPD75P3116
Program counter		12 bits	13 bits		14 bits
Program memory (bytes)		Mask ROM 4096	Mask ROM 6144	Mask ROM 8192	One-time PROM 16384
Data memory (x 4	bits)	512			
Mask options Pull-up resistor for Port 5		Available (On chip/not on chip	can be specified.)		Not available (Not on chip)
	Split resistor for LCD driving power supply				
	Wait time after RESET	Available (Selectable between	Not available (Fixed to 2 ¹⁵ /fx) ^{Note}		
	Feedback resistor of subsystem clock	Available (Use/not use can be selected.)			Not available (Enable)
Pin configuration	Pins 5 to 8	P30 to P33			P30/MD0 to P33/MD3
	Pins 10 to 13	P50 to P53	P50/D4 to P53/D7		
	Pins 14 to 17	P60/KR0 to P63/KR3	P60/KR0/D0 to P63/KR3/D3		
	Pin 21	IC	VPP		
Other		Noise resistance and noise radiation may differ due to the different circuit sizes and mask layouts.			

Note 2^{17} /fx: 21.8 ms at 6.0 MHz operation, 31.3 ms at 4.19 MHz operation 2^{15} /fx: 5.46 ms at 6.0 MHz operation, 7.81 ms at 4.19 MHz operation

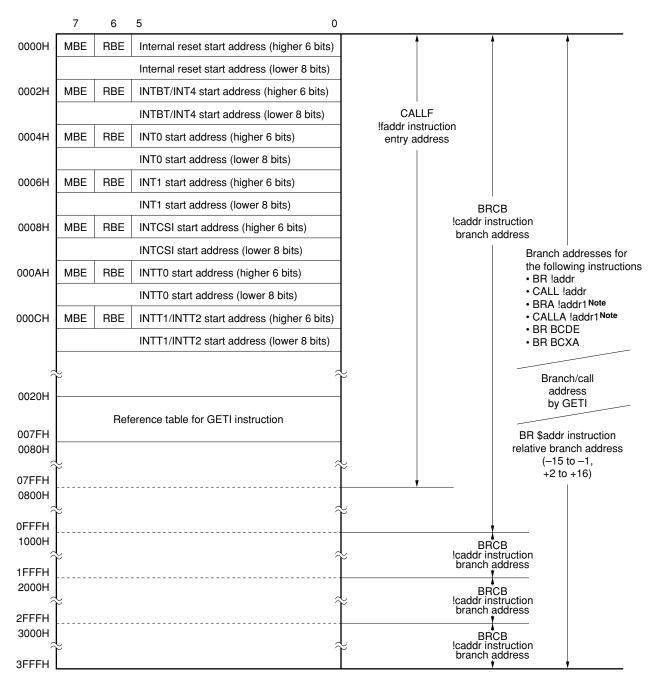
Caution There are differences in the amount of noise tolerance and noise radiation between flash memory versions and mask ROM versions. When considering changing from a flash memory version to a mask ROM version during the process from experimental manufacturing to mass production, make sure to sufficiently evaluate commercial samples (CS) (not engineering samples (ES)) of the mask ROM versions.

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6. MEMORY CONFIGURATION

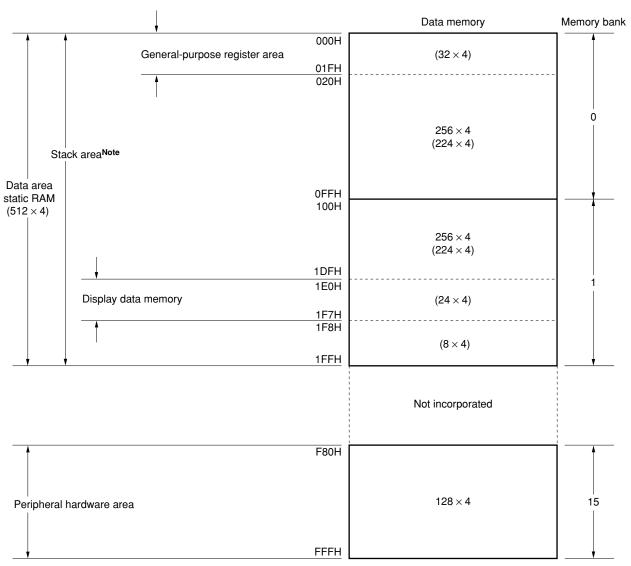
Figure 6-1. Program Memory Map



Note Can only be used in the Mk II mode.

Remark For instructions other than those noted above, the BR PCDE and BR PCXA instructions can be used to branch to addresses with changes in the PC's lower 8 bits only.

Figure 6-2. Data Memory Map



Note Memory bank 0 or 1 can be selected as the stack area.



7. INSTRUCTION SET

(1) Representation and coding formats for operands

In the instruction's operand area, use the following coding format to describe operands corresponding to the instruction's operand representations (for further details, refer to the **RA75X Assembler Package Language User's Manual (U12385E)**). When there are several codes, select and use just one. Codes that consist of uppercase letters and + or – symbols are keywords that should be entered as they are.

For immediate data, enter an appropriate numerical value or label.

Enter register flag symbols as label descriptors instead of mem, fmem, pmem, bit, etc. (for further details, refer to the **User's Manual**). The number of labels that can be entered for fmem and pmem are restricted.

Representation	Coding Format
reg	X, A, B, C, D, E, H, L
reg1	X, B, C, D, E, H, L
rp	XA, BC, DE, HL
rp1	BC, DE, HL
rp2	BC, DE
rp'	XA, BC, DE, HL, XA', BC', DE', HL'
rp'1	BC, DE, HL, XA', BC', DE', HL'
rpa	HL, HL+, HL-, DE, DL
rpa1	DE, DL
n4	4-bit immediate data or label
n8	8-bit immediate data or label
mem	8-bit immediate data or label ^{Note}
bit	2-bit immediate data or label
fmem	FB0H to FBFH, FF0H to FFFH immediate data or label
pmem	FC0H to FFFH immediate data or label
addr	0000H to 3FFFH immediate data or label
addr1	0000H to 3FFFH immediate data or label (Mk II mode only)
caddr	12-bit immediate data or label
faddr	11-bit immediate data or label
taddr	20H to 7FH immediate data (however, bit 0 = 0) or label
PORTn	Port 0 to Port 3, Port 5, Port 6, Port 8, Port 9
IExxx	IEBT, IECSI, IET0 to IET2, IE0 to IE2, IE4, IEW
RBn	RB0 to RB3
MBn	MB0, MB1, MB15

Note When processing 8-bit data, only even-numbered addresses can be specified.

(2) Operation conventions

A: A register; 4-bit accumulator

B: B register
C: C register
D: D register
E: E register
H: H register
L: L register
X: X register

XA: Register pair (XA); 8-bit accumulator

BC: Register pair (BC)
DE: Register pair (DE)
HL: Register pair (HL)

XA': Expansion register pair (XA')BC': Expansion register pair (BC')DE': Expansion register pair (DE')HL': Expansion register pair (HL')

PC: Program counter SP: Stack pointer

CY: Carry flag; bit accumulator
PSW: Program status word
MBE: Memory bank enable flag
RBE: Register bank enable flag
PORTn: Port n (n = 0 to 3, 5, 6, 8, 9)
IME: Interrupt master enable flag
IPS: Interrupt priority selection register

IExx: Interrupt enable flag

RBS: Register bank selection register MBS: Memory bank selection register PCC: Processor clock control register : Delimiter for address and bit (xx): Data addressed with xx H: Hexadecimal data



(3) Description of symbols used in addressing area

		,
*1	MB = MBE • MBS	1
_ '	MBS = 0, 1, 15	
*2	MB = 0	
	MBE = 0: MB = 0 (000H to 07FH)	
*3	MB = 15 (F80H to FFFH)	Data memory addressing
3	MBE = 1: MB = MBS	dan seemig
	MBS = 0, 1, 15	
*4	MB = 15, fmem = FB0H to FBFH, FF0H to FFFH	
*5	MB = 15, pmem = FC0H to FFFH	
*6	addr = 0000H to 3FFFH	
*7	addr, addr1 = (Current PC) - 15 to (Current PC) - 1	
	(Current PC) + 2 to (Current PC) + 16	
	caddr = 0000H to 0FFFH (PC13, 12 = 00B) or	
	1000H to 1FFFH (PC13, 12 = 01B) or	Program memory
*8	2000H to 2FFFH (PC13, 12 = 10B) or	addressing
	3000H to 3FFFH (PC13, 12 = 11B)	
*9	faddr = 0000H to 07FFH	
*10	taddr = 0020H to 007FH	
*11	addr1 = 0000H to 3FFFH (Mk II mode only)	

Remarks 1. MB indicates access-enabled memory banks.

- 2. In area *2, MB = 0 for both MBE and MBS.
- 3. In areas *4 and *5, MB = 15 for both MBE and MBS.
- 4. Areas *6 to *11 indicate corresponding address-enabled areas.

(4) Description of machine cycles

S indicates the number of machine cycles required for skipping skip-specified instructions. The value of S varies as shown below.

- Skipped instruction is 1-byte or 2-byte instruction S = 1

Note 3-byte instructions: BR !addr, BRA !addr1, CALL !addr, and CALLA !addr1

Caution The GETI instruction is skipped for one machine cycle.

One machine cycle equals one cycle (= tcy) of the CPU clock Φ . Use the PCC setting to select from among four cycle times.



Instruction Group	Mnemonic	Operand	No. of Bytes	Machine Cycle	Operation	Addressing Area	Skip Condition
Transfer	MOV	A, #n4	1	1	A ← n4		String-effect A
		reg1, #n4	2	2	reg1 ← n4		
		XA, #n8	2	2	XA ← n8		String-effect A
		HL, #n8	2	2	HL ← n8		String-effect B
		rp2, #n8	2	2	rp2 ← n8		
		A, @HL	1	1	$A \leftarrow (HL)$	*1	
		A, @HL+	1	2+S	$A \leftarrow (HL)$, then $L \leftarrow L+1$	*1	L = 0
		A, @HL-	1	2+S	$A \leftarrow (HL)$, then $L \leftarrow L-1$	*1	L = FH
		A, @rpa1	1	1	A ← (rpa1)	*2	
		XA, @HL	2	2	$XA \leftarrow (HL)$	*1	
		@HL, A	1	1	(HL) ← A	*1	
		@HL, XA	2	2	(HL) ← XA	*1	
		A, mem	2	2	$A \leftarrow (mem)$	*3	
		XA, mem	2	2	XA ← (mem)	*3	
		mem, A	2	2	(mem) ← A	*3	
		mem, XA	2	2	(mem) ← XA	*3	
		A, reg	2	2	A ← reg		
		XA, rp'	2	2	XA ← rp'		
		reg1, A	2	2	reg1 ← A		
		rp'1, XA	2	2	rp'1 ← XA		
	XCH	A, @HL	1	1	$A \longleftrightarrow (HL)$	*1	
		A, @HL+	1	2+S	$A \longleftrightarrow (HL)$, then $L \leftarrow L+1$	*1	L = 0
		A, @HL-	1	2+S	$A \longleftrightarrow (HL)$, then $L \leftarrow L-1$	*1	L = FH
		A, @rpa1	1	1	$A \longleftrightarrow (rpa1)$	*2	
		XA, @HL	2	2	$XA \longleftrightarrow (HL)$	*1	
		A, mem	2	2	$A \longleftrightarrow (mem)$	*3	
		XA, mem	2	2	$XA \longleftrightarrow (mem)$	*3	
		A, reg1	1	1	$A \longleftrightarrow reg1$		
		XA, rp'	2	2	$XA \longleftrightarrow rp'$		
Table	MOVT	XA, @PCDE	1	3	XA ← (PC13-8+DE)ROM		
reference		XA, @PCXA	1	3	XA ← (PC13-8+XA)ROM		
		XA, @BCDENote	1	3	XA ← (BCDE)ROM	*6	
		XA, @BCXA ^{Note}	1	3	XA ← (BCXA)ROM	*6	

Note Only the lower 3 bits in the B register are valid.



Instruction Group	Mnemonic	Operand	No. of Bytes	Machine Cycle	Operation	Addressing Area	Skip Condition
Bit transfer	MOV1	CY, fmem.bit	2	2	$CY \leftarrow (fmem.bit)$	*4	
		CY, pmem.@L	2	2	$CY \leftarrow (pmem7-2+L3-2.bit(L1-0))$	*5	
		CY, @H+mem.bit	2	2	CY ← (H+mem3-0.bit)	*1	
		fmem.bit, CY	2	2	(fmem.bit) ← CY	*4	
		pmem.@L, CY	2	2	$(pmem7-2+L3-2.bit(L1-0)) \leftarrow CY$	*5	
		@H+mem.bit, CY	2	2	(H+mem₃-o.bit) ← CY	*1	
Arithmetic	ADDS	A, #n4	1	1+S	A ← A+n4		carry
		XA, #n8	2	2+S	XA ← XA+n8		carry
		A, @HL	1	1+S	$A \leftarrow A+(HL)$	*1	carry
		XA, rp'	2	2+S	$XA \leftarrow XA + rp'$		carry
		rp'1, XA	2	2+S	rp'1 ← rp'1+XA		carry
	ADDC	A, @HL	1	1	$A, CY \leftarrow A+(HL)+CY$	*1	
		XA, rp'	2	2	$XA, CY \leftarrow XA+rp'+CY$		
		rp'1, XA	2	2	$rp'1, CY \leftarrow rp'1+XA+CY$		
	SUBS	A, @HL	1	1+S	$A \leftarrow A-(HL)$	*1	borrow
		XA, rp'	2	2+S	XA ← XA–rp'		borrow
		rp'1, XA	2	2+S	rp'1 ← rp'1–XA		borrow
	SUBC	A, @HL	1	1	A, CY ← A–(HL)–CY	*1	
		XA, rp'	2	2	XA, CY ← XA–rp'–CY		
		rp'1, XA	2	2	rp'1, CY ← rp'1–XA–CY		
	AND	A, #n4	2	2	A ← A ∧ n4		
		A, @HL	1	1	A ← A ∧ (HL)	*1	
		XA, rp'	2	2	$XA \leftarrow XA \wedge rp'$		
		rp'1, XA	2	2	rp'1 ← rp'1 ∧ XA		
	OR	A, #n4	2	2	A ← A v n4		
		A, @HL	1	1	$A \leftarrow A \vee (HL)$	*1	
		XA, rp'	2	2	XA ← XA v rp'		
		rp'1, XA	2	2	rp'1 ← rp'1 v XA		
	XOR	A, #n4	2	2	A ← A ₩ n4		
		A, @HL	1	1	$A \leftarrow A \forall (HL)$	*1	
		XA, rp'	2	2	XA ← XA ₩ rp'		
		rp'1, XA	2	2	rp'1 ← rp'1 ₩ XA		
Accumulator	RORC	Α	1	1	$CY \leftarrow A_0, A_3 \leftarrow CY, A_{n-1} \leftarrow A_n$		
manipulation	NOT	A	2	2	$A \leftarrow \overline{A}$		
Increment/	INCS	reg	1	1+S	reg ← reg+1		reg = 0
decrement		rp1	1	1+S	rp1 ← rp1+1		rp1 = 00H
		@HL	2	2+S	(HL) ← (HL)+1	*1	(HL) = 0
		mem	2	2+S	$(mem) \leftarrow (mem)+1$	*3	(mem) = 0
	DECS	reg	1	1+S	reg ← reg-1		reg = FH
		rp'	2	2+S	rp' ← rp'–1		rp' = FFH



Instruction Group	Mnemonic	Operand	No. of Bytes	Machine Cycle	Operation	Addressing Area	Skip Condition
Comparison	SKE	reg, #n4	2	2+S	Skip if reg=n4		reg = n4
		@HL, #n4	2	2+S	Skip if (HL)=n4	*1	(HL) = n4
		A, @HL	1	1+S	Skip if A=(HL)	*1	A = (HL)
		XA, @HL	2	2+S	Skip if XA=(HL)	*1	XA = (HL)
		A, reg	2	2+S	Skip if A=reg		A = reg
		XA, rp'	2	2+S	Skip if XA=rp'		XA = rp'
Carry flag	SET1	CY	1	1	CY ← 1		
manipulation	CLR1	CY	1	1	CY ← 0		
	SKT	CY	1	1+S	Skip if CY=1		CY = 1
	NOT1	CY	1	1	$CY \leftarrow \overline{CY}$		
Memory bit	SET1	mem.bit	2	2	(mem.bit) ← 1	*3	
manipulation		fmem.bit	2	2	(fmem.bit) ← 1	*4	
		pmem.@L	2	2	$(pmem_{7-2}+L_{3-2}.bit(L_{1-0})) \leftarrow 1$	*5	
		@H+mem.bit	2	2	(H+mem₃-o.bit) ← 1	*1	
	CLR1	mem.bit	2	2	(mem.bit) ← 0	*3	
		fmem.bit	2	2	$(fmem.bit) \leftarrow 0$	*4	
		pmem.@L	2	2	$(pmem7-2+L3-2.bit(L1-0)) \leftarrow 0$	*5	
		@H+mem.bit	2	2	(H+mem₃-o.bit) ← 0	*1	
	SKT	mem.bit	2	2+S	Skip if(mem.bit)=1	*3	(mem.bit) = 1
		fmem.bit	2	2+S	Skip if(fmem.bit)=1	*4	(fmem.bit) = 1
		pmem.@L	2	2+S	Skip if(pmem7-2+L3-2.bit(L1-0))=1	*5	(pmem.@L) = 1
		@H+mem.bit	2	2+S	Skip if(H+mem3-0.bit)=1	*1	(@H+mem.bit) =
	SKF	mem.bit	2	2+S	Skip if(mem.bit)=0	*3	(mem.bit) = 0
		fmem.bit	2	2+S	Skip if(fmem.bit)=0	*4	(fmem.bit) = 0
		pmem.@L	2	2+S	Skip if(pmem7-2+L3-2.bit(L1-0))=0	*5	(pmem.@L) = 0
		@H+mem.bit	2	2+S	Skip if(H+mem3-0.bit)=0	*1	(@H+mem.bit) =
	SKTCLR	fmem.bit	2	2+S	Skip if(fmem.bit)=1 and clear	*4	(fmem.bit) = 1
		pmem.@L	2	2+S	Skip if(pmem7-2+L3-2.bit(L1-0))=1 and clear	*5	(pmem.@L) = 1
		@H+mem.bit	2	2+S	Skip if(H+mem3-0.bit)=1 and clear	*1	(@H+mem.bit) =
	AND1	CY, fmem.bit	2	2	CY ← CY ∧ (fmem.bit)	*4	
		CY, pmem.@L	2	2	$CY \leftarrow CY \land (pmem7-2+L3-2.bit(L1-0))$	*5	
		CY, @H+mem.bit	2	2	CY ← CY ∧ (H+mem₃-o.bit)	*1	
	OR1	CY, fmem.bit	2	2	CY ← CY v (fmem.bit)	*4	
		CY, pmem.@L	2	2	$CY \leftarrow CY \text{ v (pmem7-2+L3-2.bit(L1-0))}$	*5	
		CY, @H+mem.bit	2	2	CY ← CY v (H+mem3-0.bit)	*1	
	XOR1	CY, fmem.bit	2	2	CY ← CY ♥ (fmem.bit)	*4	
		CY, pmem.@L	2	2	CY ← CY ♥ (pmem7-2+L3-2.bit(L1-0))	*5	
		CY, @H+mem.bit	2	2	CY ← CY ♥ (H+mem3-0.bit)	*1	

Instruction Group	Mnemonic	Operand	No. of Bytes	Machine Cycle	Operation	Addressing Area	Skip Condition
Branch	BR ^{Note 1} addr		_	_	PC13-0 ← addr Use the assembler to select the most appropriate instruction among the following. • BR !addr • BRCB !caddr • BR \$addr	*6	
		addr1	_	_	PC13-0 ← addr1 Use the assembler to select the most appropriate instruction among the following. • BRA !addr1 • BR !addr • BRCB !caddr • BR \$addr1	*11	
		!addr	3	3	PC13-0 ← addr	*6	
		\$addr	1	2	PC13-0 ← addr	*7	
		\$addr1	1	2	PC13-0 ← addr1		
		PCDE	2	3	PC13-0 ← PC13-8+DE		
		PCXA	2	3	PC13-0 ← PC13-8+XA		
		BCDE	2	3	$PC13-0 \leftarrow BCDE^{Note 2}$	*6	
		BCXA	2	3	PC13-0 ← BCXA ^{Note 2}	*6	
	BRA ^{Note 1}	!addr1	3	3	PC13-0 ← addr1	*11	
	BRCB	!caddr	2	2	PC13-0 ← PC13, 12+caddr11-0	*8	

Notes 1. The sections in double boxes are only supported in the Mk II mode. The other sections are only supported in the MK I mode.

2. Only the lower two bits in the B register are valid.

Instruction Group	Mnemonic	Operand	No. of Bytes	Machine Cycle	Operation	Addressing Area	Skip Condition
Subroutine	CALLANote	!addr1	3	3	(SP-6)(SP-3)(SP-4) ← PC11-0	*11	
tack control					(SP–5) ← 0, 0, PC13, 12		
					(SP−2) ← X, X, MBE, RBE		
					PC13-0 ← addr1, SP ← SP-6		
	CALLNote	!addr	3	3	(SP-4)(SP-1)(SP-2) ← PC ₁₁₋₀	*6	
					$(SP-3) \leftarrow MBE, RBE, PC13, 12$		
					$PC_{13-0} \leftarrow addr, SP \leftarrow SP-4$		
				4	(SP-6)(SP-3)(SP-4) ← PC11-0		
					(SP–5) ← 0, 0, PC13, 12		
					$(SP-2) \leftarrow X, X, MBE, RBE$		
					$PC_{13-0} \leftarrow addr, SP \leftarrow SP-6$		
	CALLF ^{Note}	!faddr	2	2	(SP-4)(SP-1)(SP-2) ← PC ₁₁₋₀	*9	
					(SP–3) ← MBE, RBE, PC13, 12		
					PC13-0 ← 000+faddr, SP ← SP–4		
				3	(SP-6)(SP-3)(SP-4) ← PC11-0	Ī	
					(SP–5) ← 0, 0, PC13, 12		
					(SP–2) ← X, X, MBE, RBE		
					PC ₁₃₋₀ ← 000+faddr, SP ← SP–6		
	RET ^{Note}		1	3	MBE, RBE, PC13, 12 ← (SP+1)		
					PC11-0 ← (SP)(SP+3)(SP+2)		
					SP ← SP+4		
					X, X, MBE, RBE ← (SP+4)		
					$ PC_{11-0} \leftarrow (SP)(SP+3)(SP+2) $		
					0, 0, PC13, 12 ← (SP+1)		
					SP ← SP+6		
	RETSNote		1	3+S	MBE, RBE, PC13, 12 ← (SP+1)	1	Unconditional
					PC11-0 ← (SP)(SP+3)(SP+2)		
					SP ← SP+4		
					then skip unconditionally		
					X, X, MBE, RBE ← (SP+4)		
					$ PC_{11-0} \leftarrow (SP)(SP+3)(SP+2) $		
					0, 0, PC13, 12 ← (SP+1)		
					 SP ← SP+6		
					then skip unconditionally		
	RETI ^{Note}		1	3	MBE, RBE, PC13, 12 ← (SP+1)	J	
					$PC_{11-0} \leftarrow (SP)(SP+3)(SP+2)$		
					PSW ← (SP+4)(SP+5)		
					SP ← SP+6		
					0, 0, PC13, 12 ← (SP+1)	Ī	
					$PC_{11-0} \leftarrow (SP)(SP+3)(SP+2)$		
					PSW ← (SP+4)(SP+5), SP ← SP+6		

Note The sections in double boxes are only supported in the Mk II mode. The other sections are only supported in the Mk I mode.



Machine Cycle	Operation	Addressing Area	Skip Condition
1	$(SP-1)(SP-2) \leftarrow rp, SP \leftarrow SP-2$		
2	$ \begin{array}{l} (SP1) \leftarrow MBS, (SP2) \leftarrow RBS,\\ SP \leftarrow SP2 \end{array} $		
1	$rp \leftarrow (SP+1)(SP), SP \leftarrow SP+2$		
2	$MBS \leftarrow (SP+1),RBS \leftarrow (SP),SP \leftarrow SP+2$		
2	IME(IPS.3) ← 1		
2	IExxx ← 1		
2	$IME(IPS.3) \leftarrow 0$		
2	IExxx ← 0		
2	A ← PORTn (n=0 to 3, 5, 6, 8, 9)		
2	$XA \leftarrow PORTn+1$, $PORTn (n=8)$		
2	PORTn ← A (n=2 to 3, 5, 6, 8, 9)		
2	PORTn+1, PORTn ← XA (n=8)		
2	Set HALT Mode(PCC.2 ← 1)		
2	Set STOP Mode(PCC.3 ← 1)		
1	No Operation		
2	RBS ← n (n=0 to 3)		
2	MBS ← n (n=0, 1, 15)		
3	When using TBR instruction	*10	
	PC13-0 ← (taddr)5-0+(taddr+1)		
	When using TCALL instruction		
	(SP-4)(SP-1)(SP-2) ← PC11-0		
	(SP–3) ← MBE, RBE, PC13, 12		
	PC13-0 ← (taddr)5-0+(taddr+1)		
	SP ← SP–4		
	When using instruction other than TBR or TCALL Execute (taddr)(taddr+1) instructions		Determined by referenced instruction
3	When using TBR instruction	*10	
	PC13-0 ← (taddr)5-0+(taddr+1)		
4	When using TCALL instruction		
	(SP-6)(SP-3)(SP-4) ← PC11-0		
	(SP-5) ← 0, 0, PC13, 12		
	$(SP-2) \leftarrow X, X, MBE, RBE$		
	$PC_{13-0} \leftarrow (taddr)_{5-0} + (taddr+1)$		
	SP ← SP-6		
3	When using instruction other than TBR or TCALL		Determined by referenced instruction
3		SP ← SP–6 • When using instruction other than	SP ← SP–6 • When using instruction other than TBR or TCALL

Notes 1. Setting MBE = 0 or MBE = 1, MBS = 15 is required during the execution of the IN or OUT instruction.

- 2. The TBR and TCALL instructions are assembler quasi-directives for the GETI instruction table definitions.
- 3. The sections in double boxes are only supported in the Mk II mode. The other sections are only supported in the Mk I mode.

8. ONE-TIME PROM (PROGRAM MEMORY) WRITE AND VERIFY

The program memory contained in the μ PD75P3116 is a 16384 × 8-bit one-time PROM that can be electrically written one time only. The pins listed in the table below are used for this PROM's write/verify operations. Clock input from the X1 pin is used instead of address input as a method for updating addresses.

Pin	Function
VPP	Pin where program voltage is applied during program memory write/verify (usually VDD potential)
X1, X2	Clock input pins for address updating during program memory write/verify. Input the X1 pin's inverted signal to the X2 pin.
MD0 to MD3	Operation mode selection pin for program memory write/verify
D0/P60 to D3/P63 (lower 4 bits) D4/P50 to D7/P53 (higher 4 bits)	8-bit data I/O pins for program memory write/verify
VDD	Pin where power supply voltage is applied. Apply 1.8 to 5.5 V in normal operation mode and +6 V for program memory write/verify.

Caution Pins not used for program memory write/verify should be connected to Vss.

8.1 Operation Modes for Program Memory Write/Verify

When +6 V is applied to the V_{DD} pin and +12.5 V to the V_{PP} pin, the μ PD75P3116 enters the program memory write/verify mode. The following operation modes can be specified by setting pins MD0 to MD3 as shown below.

Operation Mode Specification						Operation Mode
VPP	VDD	MD0	MD1	MD2	MD3	
+12.5 V	+6 V	Н	L	Н	L	Zero-clear program memory address
		L	Н	Н	Н	Write mode
		L	L	Н	Н	Verify mode
		Н	×	Н	Н	Program inhibit mode

 \times : L or H

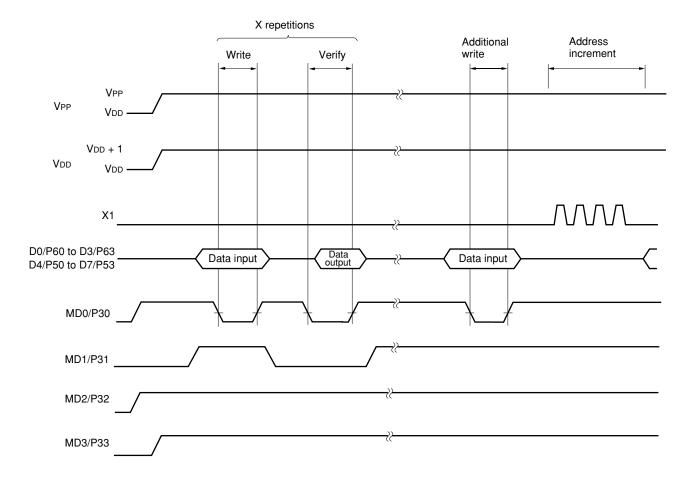


8.2 Program Memory Write Procedure

Program memory can be written at high speed using the following procedure.

- (1) Pull down unused pins to Vss via resistors. Set the X1 pin to low.
- (2) Supply 5 V to the VDD and VPP pins.
- (3) Wait 10 μ s.
- (4) Select the program memory address zero-clear mode.
- (5) Supply 6 V to VDD and 12.5 V to VPP.
- (6) Write data in the 1 ms write mode.
- (7) Select the verify mode. If the data is written, go to (8) and if not, repeat (6) and (7).
- (8) Additional write. (X: Number of write operations from (6) and (7)) \times 1 ms
- (9) Apply four pulses to the X1 pin to increment the program memory address by one.
- (10) Repeat (6) to (9) until the end address is reached.
- (11) Select the program memory address zero-clear mode.
- (12) Return the VDD- and VPP-pin voltages to 5 V.
- (13) Turn off the power.

The following figure shows steps (2) to (9).



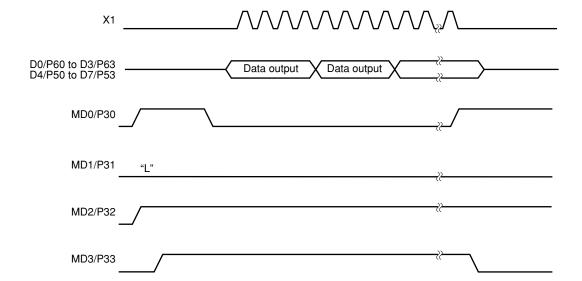
8.3 Program Memory Read Procedure

The μ PD75P3116 can read program memory contents using the following procedure.

- (1) Pull down unused pins to Vss via resistors. Set the X1 pin to low.
- (2) Supply 5 V to the VDD and VPP pins.
- (3) Wait 10 μ s.
- (4) Select the program memory address zero-clear mode.
- (5) Supply 6 V to VDD and 12.5 V to VPP.
- (6) Select the verify mode. Apply four pulses to the X1 pin. The data stored in one address will be output every four clock pulses.
- (7) Select the program memory address zero-clear mode.
- (8) Return the VDD- and VPP-pin voltages to 5 V.
- (9) Turn off the power.

The following figure shows steps (2) to (7).





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8.4 One-Time PROM Screening

Due to its structure, the one-time PROM cannot be fully tested before shipment by NEC Electronics. Therefore, NEC Electronics recommends that after the required data is written and the PROM is stored under the temperature and time conditions shown below, the PROM should be verified via screening.

Storage Temperature	Storage Time
125°C	24 hours

NEC Electronics offers QTOP microcontrollers for which one-time PROM writing, marking, screening, and verification are provided at additional cost. For further details, contact an NEC Electronics sales representative.



9. ELECTRICAL SPECIFICATIONS

Absolute Maximum Ratings (T_A = 25°C)

Parameter	Symbol	Test Conditions	Rating	Unit
Power supply voltage	V _{DD}		-0.3 to +7.0	٧
PROM power supply voltage	VPP		-0.3 to +13.5	V
Input voltage	VII	Except port 5	-0.3 to V _{DD} + 0.3	٧
	V _{I2}	Port 5 (N-ch open drain)	-0.3 to +14	V
Output voltage	Vo		-0.3 to V _{DD} + 0.3	V
Output current, high	Іон	Per pin	-10	mA
		Total of all pins	-30	mA
Output current, low	loL	Per pin	30	mA
		Total of all pins	220	mA
Operating ambient temperature	Та		-40 to +85 ^{Note}	°C
Storage temperature	T _{stg}		-65 to +150	°C

Note When LCD is driven in normal mode: $T_A = -10 \text{ to } +85^{\circ}\text{C}$

Caution Product quality may suffer if the absolute maximum rating is exceeded even momentarily for any parameter. That is, the absolute maximum ratings are rated values at which the product is on the verge of suffering physical damage, and therefore the product must be used under conditions that ensure that the absolute maximum ratings are not exceeded.

Capacitance ($T_A = 25^{\circ}C$, $V_{DD} = 0 V$)

Parameter	Symbol	Test Conditions	MIN.	TYP.	MAX.	Unit
Input capacitance	Cin	f = 1 MHz			15	pF
Output capacitance	Соит	Unmeasured pins returned to 0 V.			15	pF
I/O capacitance	Сю				15	pF



Main System Clock Oscillator Characteristics (TA = -40 to +85°C, VDD = 1.8 to 5.5 V)

Resonator	Recommended Constant	Parameter	Test Conditions	MIN.	TYP.	MAX.	Unit
Ceramic	X1 X2	Oscillation		1.0		6.0 ^{Note 2}	MHz
resonator		frequency (fx)Note 1					
	C1 + C2	Oscillation	After V _{DD} reaches oscil-			4	ms
	V _{DD}	stabilization timeNote 3	lation voltage range MIN.				
Crystal	X1 X2	Oscillation		1.0		6.0 ^{Note 2}	MHz
resonator		frequency (fx)Note 1					
	C1	Oscillation	V _{DD} = 4.5 to 5.5 V			10	ms
	V _{DD}	stabilization timeNote 3	V _{DD} = 1.8 to 5.5 V			30	
External		X1 input		1.0		6.0 ^{Note 2}	MHz
clock	X1 X2	frequency (fx)Note 1					
		X1 input		83.3		500	ns
	7	high-/low-level width (tхн, tхь)					

- Notes 1. Indicates only oscillator characteristics. Refer to AC Characteristics for instruction execution time.
 - 2. When the power supply voltage is 1.8 V \leq VDD < 2.7 V and the oscillation frequency is 4.19 MHz < fx \leq 6.0 MHz, setting the processor clock control register (PCC) to 0011 makes 1 machine cycle less than the required 0.95 μ s. Therefore, set PCC to a value other than 0011.
 - **3.** The oscillation stabilization time is necessary for oscillation to stabilize after applying V_{DD} or releasing the STOP mode.

Caution When using the main system clock oscillator, wire as follows in the area enclosed by the broken lines in the above figures to avoid an adverse effect from wiring capacitance.

- · Keep the wiring length as short as possible.
- Do not cross the wiring with the other signal lines.
- · Do not route the wiring near a signal line through which a high fluctuating current flows.
- Always make the ground point of the oscillator capacitor the same potential as VDD.
- · Do not ground the capacitor to a ground pattern through which a high current flows.
- Do not fetch signals from the oscillator.



Subsystem Clock Oscillator Characteristics (TA = -40 to +85°C, VDD = 1.8 to 5.5 V)

Resonator	Recommended Constant	Parameter	Test Conditions	MIN.	TYP.	MAX.	Unit
Crystal	XT1 XT2	Oscillation		32	32.768	35	kHz
resonator	R	frequency (fxT)Note 1					
	C3 + III + C4	Oscillation	V _{DD} = 4.5 to 5.5 V		1.0	2	s
	V _{DD}	stabilization timeNote 2	V _{DD} = 1.8 to 5.5 V			10	
External		XT1 input frequency		32		100	kHz
clock	XT1 XT2	(fxT)Note 1					
		XT1 input high-/low-level		5		15	μs
		width (txтн, txть)					

- Notes 1. Indicates only oscillator characteristics. Refer to AC Characteristics for instruction execution time.
 - 2. The oscillation stabilization time is necessary for oscillation to stabilize after applying VDD.

Caution When using the subsystem clock oscillator, wire as follows in the area enclosed by the broken lines in the above figures to avoid an adverse effect from wiring capacitance.

- · Keep the wiring length as short as possible.
- · Do not cross the wiring with the other signal lines.
- Do not route the wiring near a signal line through which a high fluctuating current flows.
- · Always make the ground point of the oscillator capacitor the same potential as VDD.
- Do not ground the capacitor to a ground pattern through which a high current flows.
- · Do not fetch signals from the oscillator.

The subsystem clock oscillator is designed as a low amplification circuit to provide low consumption current, and is more liable to misoperation by noise than the main system clock oscillator. Special care should therefore be taken regarding the wiring method when the subsystem clock is used.



DC Characteristics (TA = -40 to $+85^{\circ}$ C, VDD = 1.8 to 5.5 V)

Parameter	Symbol	Test Conditions				TYP.	MAX.	Unit
Output current, low	loL	Per pin					15	mA
		Total of all pins					150	mA
Input voltage, high	V _{IH1}	Ports 2, 3, 8	, and 9	$2.7 \le V_{DD} \le 5.5 V$	0.7V _{DD}		V _{DD}	٧
				$1.8 \le V_{DD} < 2.7 V$	0.9V _{DD}		V _{DD}	V
	V _{IH2}	Ports 0, 1, 6, RESET		$2.7 \le V_{DD} \le 5.5 V$	0.8V _{DD}		V _{DD}	٧
				1.8 ≤ V _{DD} < 2.7 V	0.9V _{DD}		V _{DD}	V
	VIH3	Port 5 2.7 ≤ V _{DD} ≤ 5.5 V		0.7V _{DD}		13	٧	
		(N-ch open-drain) $1.8 \le V_{DD} < 2.7 \text{ V}$		0.9V _{DD}		13	٧	
	V _{IH4}	X1, XT1			V _{DD} - 0.1		V _{DD}	V
Input voltage, low	VIL1			$2.7 \le V_{DD} \le 5.5 V$	0		0.3V _{DD}	V
				1.8 ≤ V _{DD} < 2.7 V	0		0.1 V _{DD}	٧
	V _{IL2}	Ports 0, 1, 6	, RESET	$2.7 \le V_{DD} \le 5.5 V$	0		0.2V _{DD}	V
				1.8 ≤ V _{DD} < 2.7 V	0		0.1V _{DD}	V
	V _{IL3}	X1, XT1			0		0.1	V
Output voltage, high	Vон	SCK, SO, Po	rts 2, 3, 6, 8, and 9	он = −1.0 mA	V _{DD} - 0.5			V
Output voltage, low	V _{OL1}	SCK, SO, Ports 2, 3, 5, 6, 8, and 9		IoL = 15 mA, V _{DD} = 4.5 to 5.5 V		0.2	2.0	٧
				IoL = 1.6 mA			0.4	V
	V _{OL2}	SB0, SB1	When N-ch open-drapull-up resistor ≥ 1			0.2V _{DD}	V	
Input leakage	Ішн1	VIN = VDD	V _{DD} Pins other than X1, XT1 X1, XT1				3	μΑ
current, high	I LIH2						20	μΑ
	Ілнз	VIN = 13 V	Port 5 (N-ch open-drain)				20	μΑ
Input leakage	ILIL1	Vin = 0 V	Pins other than X1,	XT1, and Port 5			-3	μΑ
current, low	ILIL2		X1, XT1				-20	μΑ
	ILIL3		Port 5 (N-ch open-drain) When another instruction than input instruction is executed				-3	μΑ
			Port 5	V _{DD} = 1.8 to 5.5 V			-30	μΑ
			(N-ch open-drain) When input	V _{DD} = 5.0 V		-10	-27	μΑ
			instruction is executed	V _{DD} = 3.0 V		-3	-8	μΑ
Output leakage	ILOH1	Vout = Vdd	SCK, SO/SB0, SB1, Ports 2, 3, 6, 8, and 9				3	μΑ
current, high	ILOH2	Vout = 13 V	Port 5 (N-ch open-drain)				20	μΑ
Output leakage current, low	ILOL	Vout = 0 V				-3	μΑ	
On-chip pull-up resistor	R∟	VIN = 0 V	Ports 0, 1, 2, 3, 6, 8 (Excluding P00 pin)	50	100	200	kΩ	



DC Characteristics ($T_A = -40 \text{ to } +85^{\circ}\text{C}$, $V_{DD} = 1.8 \text{ to } 5.5 \text{ V}$)

Parameter	Symbol	Test Conditions			MIN.	TYP.	MAX.	Unit	
LCD drive voltage	VLCD	VAC0 = 0	T _A = -10 to +85°C		2.7		V _{DD}	V	
					2.2		V _{DD}	V	
		VAC0 = 1			1.8		V _{DD}	V	
VAC currentNote 1	Ivac	VAC0 = 1, VDD =	2.0 V ±10%				1	4	μΑ
LCD output voltage deviationNote 2 (common)	Vodc	Io = ±1.0 μA	VLCD0 = VLCD VLCD1 = VLCD >	VLCD0 = VLCD VLCD1 = VLCD × 2/3				±0.2	V
LCD output voltage deviationNote 2 (segment)	Vods	lo = ±0.5 μA	$V_{LCD2} = V_{LCD} > 1.8 V \le V_{LCD} > 1.8 V \le V_{LCD} > 1.8 V_{LCD} >$			0		±0.2	V
Supply currentNote 3	I _{DD1}	6.00 MHz ^{Note 4}	V _{DD} = 5.0 V ±	V ±10%Note 5			3.2	9.5	mA
		Crystal oscillation	V _{DD} = 3.0 V ±	10%Note 6			0.55	1.6	mA
	I _{DD2}	C1 = C2 = 22 pF	HALT mode	V _{DD} = 5.0	V ±10%		0.7	2.0	mA
				V _{DD} = 3.0 V ±10%			0.25	0.8	mA
	I _{DD1}	4.19 MHz ^{Note 4}	V _{DD} = 5.0 V ±	10%Note 5			2.5	7.5	mA
		Crystal oscillation	V _{DD} = 3.0 V ±	10%Note 6			0.45	1.35	mA
	I _{DD2}	C1 = C2 = 22 pF	HALT mode	V _{DD} = 5.0 V ±10%			0.65	1.8	mA
				V _{DD} = 3.0 V ±10%	V ±10%		0.22	0.7	mA
	IDD3	32.768 kHz ^{Note 7}	Low-voltage	V _{DD} = 3.0 V ±10% V _{DD} = 2.0 V ±10%			45	130	μΑ
		Crystal oscillation	mode ^{Note 8}				20	55	μΑ
				VDD = 3.0 V	, T _A = 25°C		45	90	μΑ
			Low current consumption	V _{DD} = 3.0	V ±10%		42	120	μΑ
			mode ^{Note 9} V _D	V _{DD} = 3.0 V, T _A = 25°C			42	85	μΑ
	Low current consum				V _{DD} = 3.0 V ±10%		5.5	18	μΑ
					V _{DD} = 2.0 V ±10%		2.2	7	μΑ
					VDD = 3.0 V, TA = 25°C		5.5	12	μΑ
		_	V _{DD} = 3.0 V ±10%		4.0	12	μΑ		
				consump- tion mode	V _{DD} = 3.0 V, T _A = 25°C		4.0	8	μΑ
	+10%	XT1 = 0 V ^{Note 10}	VDD = 5.0 V ±	= 5.0 V ±10%			0.05	10	μΑ
		STOP mode		$T_A = -40 \text{ to } +85^{\circ}\text{C}$			0.02	5	μΑ
		T _A = 25°C			0.02	3	μΑ		

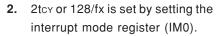
- **Notes 1.** Set to VAC0 = 0 when the low current consumption mode and the stop mode are used. If VAC0 = 1 is set, the current increases for approx. 1 μ A.
 - 2. The voltage deviation is the difference from the output voltage corresponding to the ideal value of the segment and common outputs (V_{LCDn} ; n = 0, 1, 2).
 - 3. Not including currents flowing through on-chip pull-up resistors.
 - 4. Including oscillation of the subsystem clock.
 - 5. When the processor clock control register (PCC) is set to 0011 and the device is operated in the high-speed mode.
 - **6.** When PCC is set to 0000 and the device is operated in the low-speed mode.
 - 7. When the system clock control register (SCC) is set to 1001 and the device is operated on the subsystem clock, with main system clock oscillation stopped.
 - 8. When the sub-oscillator control register (SOS) is set to 0000.
 - 9. When SOS is set to 0010.
 - 10. When SOS is set to 00×1 and the feedback resistor of the sub-oscillator is not used (x: Don't care).

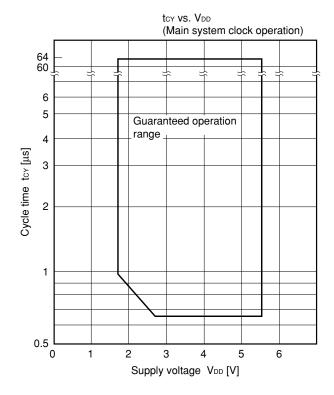


AC Characteristics	$(T_A = -40 \text{ to } +85^{\circ}C)$	$, V_{DD} = 1.8 \text{ to } 5.5 \text{ V})$
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Parameter	Symbol	Test Co	onditions	MIN.	TYP.	MAX.	Unit
CPU clock cycle	tcy	Operating on	V _{DD} = 2.7 to 5.5 V	0.67		64	μs
time ^{Note 1}		main system clock	V _{DD} = 1.8 to 5.5 V	0.95		64	μs
(Min. instruction execution		Operating on subsystem cl	ock	114	122	125	μs
time = 1 machine cycle)							
TI0, TI1, TI2 input	fτι	V _{DD} = 2.7 to 5.5 V		0		1.0	MHz
frequency		V _{DD} = 1.8 to 5.5 V	V _{DD} = 1.8 to 5.5 V			275	kHz
TI0, TI1, TI2 input	tтін, tті∟	V _{DD} = 2.7 to 5.5 V	V _{DD} = 2.7 to 5.5 V				μs
high-/low-level width		V _{DD} = 1.8 to 5.5 V		1.8			μs
Interrupt input high-/	tinth, tintl	INT0	IM02 = 0	Note 2			μs
low-level width			IM02 = 1	10			μs
		INT1, 2, 4		10			μs
		KR0 to KR7		10			μs
RESET low-level width	trsL			10			μs

Notes 1. The cycle time (minimum instruction execution time) of the CPU clock (Φ) is determined by the oscillation frequency of the connected resonator (and external clock), the system clock control register (SCC) and the processor clock control register (PCC). The figure on the right indicates the cycle time toy versus supply voltage VDD characteristics with the main system clock operating.







Serial Transfer Operation

2-wire and 3-wire serial I/O mode (SCK...Internal clock output): (TA = -40 to +85°C, VDD = 1.8 to 5.5 V)

Parameter	Symbol	Test Conditions			TYP.	MAX.	Unit
SCK cycle time	tkcy1	V _{DD} = 2.7 to 5.5 V		1300			ns
		V _{DD} = 1.8 to 5.5 V		3800			ns
SCK high-/low-level	tkli, tkHi	V _{DD} = 2.7 to 5.5 V		tkcy1/2-50			ns
width		V _{DD} = 1.8 to 5.5 V		tксү1/2-150			ns
SI ^{Note 1} setup time	tsıĸı	$V_{DD} = 2.7 \text{ to } 5.5 \text{ V}$		150			ns
(to SCK↑)		V _{DD} = 1.8 to 5.5 V		500			ns
SI ^{Note 1} hold time	tksi1	V _{DD} = 2.7 to 5.5 V		400			ns
(from SCK↑)		V _{DD} = 1.8 to 5.5 V	600			ns	
SO ^{Note 1} output delay	tkso1	$R_L = 1 \text{ k}\Omega,$	V _{DD} = 2.7 to 5.5 V	0		250	ns
time from SCK↓		C _L = 100 pF ^{Note 2}	V _{DD} = 1.8 to 5.5 V	0		1000	ns

Notes 1. In 2-wire serial I/O mode, read this parameter as SB0 or SB1 instead.

2. R_L and C_L are the load resistance and load capacitance of the SO output lines, respectively.

2-wire and 3-wire serial I/O mode (SCK...External clock input): (TA = -40 to +85°C, VDD = 1.8 to 5.5 V)

Parameter	Symbol	Test Conditions			TYP.	MAX.	Unit
SCK cycle time	tkcy2	V _{DD} = 2.7 to 5.5 V		800			ns
		V _{DD} = 1.8 to 5.5 V		3200			ns
SCK high-/low-level	tkl2, tkH2	V _{DD} = 2.7 to 5.5 V		400			ns
width		V _{DD} = 1.8 to 5.5 V		1600			ns
SI ^{Note 1} setup time	tsik2	V _{DD} = 2.7 to 5.5 V		100			ns
(to SCK ↑)		V _{DD} = 1.8 to 5.5 V		150			ns
SI ^{Note 1} hold time	tksi2	V _{DD} = 2.7 to 5.5 V		400			ns
(from SCK↑)		V _{DD} = 1.8 to 5.5 V	600			ns	
SO ^{Note 1} output delay	tkso2	$R_L = 1 \text{ k}\Omega,$	V _{DD} = 2.7 to 5.5 V	0		300	ns
time from SCK↓		C _L = 100 pF ^{Note 2}	V _{DD} = 1.8 to 5.5 V	0		1000	ns

Notes 1. In 2-wire serial I/O mode, read this parameter as SB0 or SB1 instead.

2. RL and CL are the load resistance and load capacitance of the SO output lines, respectively.



SBI mode (\overline{SCK} ...Internal clock output (master)): (TA = -40 to +85°C, VDD = 1.8 to 5.5 V)

Parameter	Symbol	Test Cor	nditions	MIN.	TYP.	MAX.	Unit
SCK cycle time	tkcy3	V _{DD} = 2.7 to 5.5 V		1300			ns
		V _{DD} = 1.8 to 5.5 V		3800			ns
SCK high-/low-level	tкьз, tкнз	V _{DD} = 2.7 to 5.5 V		tксүз/2-50			ns
width		V _{DD} = 1.8 to 5.5 V		tксүз/2-150			ns
SB0, 1 setup time	tsik3	V _{DD} = 2.7 to 5.5 V		150			ns
(to SCK ↑)		V _{DD} = 1.8 to 5.5 V	V _{DD} = 1.8 to 5.5 V				ns
SB0, 1 hold time (from SCK↑)	tĸsıз			tксүз/2			ns
SB0, 1 output delay	tkso3	$R_L = 1 \text{ k}\Omega,$	V _{DD} = 2.7 to 5.5 V	0		250	ns
time from SCK↓		C _L = 100 pF ^{Note}	V _{DD} = 1.8 to 5.5 V	0		1000	ns
SB0, 1↓ from SCK↑	tкsв			tксүз			ns
SCK↓ from SB0, 1↓	tsвк			tксүз			ns
SB0, 1 low-level width	tsbl			tксүз			ns
SB0, 1 high-level width	tsвн			tксүз			ns

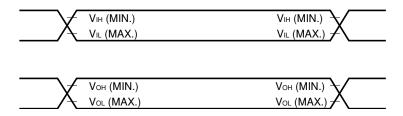
Note RL and CL are the load resistance and load capacitance of the SB0 and SB1 output lines, respectively.

SBI mode (SCK...External clock input (slave)): (TA = -40 to +85°C, VDD = 1.8 to 5.5 V)

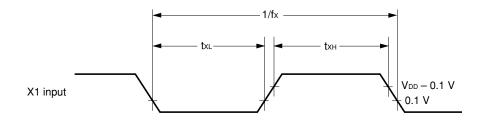
Parameter	Symbol	Test Co	nditions	MIN.	TYP.	MAX.	Unit
SCK cycle time	tkcy4	V _{DD} = 2.7 to 5.5 V		800			ns
		V _{DD} = 1.8 to 5.5 V		3200			ns
SCK high-/low-level	tkl4, tkH4	V _{DD} = 2.7 to 5.5 V		400			ns
width		V _{DD} = 1.8 to 5.5 V		1600			ns
SB0, 1 setup time	tsik4	V _{DD} = 2.7 to 5.5 V		100			ns
(to SCK ↑)		V _{DD} = 1.8 to 5.5 V	V _{DD} = 1.8 to 5.5 V				ns
SB0, 1 hold time (from SCK↑)	tksi4			tkcy4/2			ns
SB0, 1 output delay	tkso4	$R_L = 1 k\Omega$,	V _{DD} = 2.7 to 5.5 V	0		300	ns
time from SCK↓		C _L = 100 pF ^{Note}	V _{DD} = 1.8 to 5.5 V	0		1000	ns
SB0, 1↓ from SCK↑	tĸsв			tkcy4			ns
SCK↓ from SB0, 1↓	t sbk			tkcy4			ns
SB0, 1 low-level width	tsbl			tkcy4			ns
SB0, 1 high-level width	tsвн			tkcy4			ns

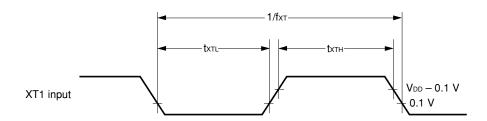
Note RL and CL are the load resistance and load capacitance of the SB0 and SB1 output lines, respectively.

AC Timing Test Points (Excluding X1, XT1 Input)

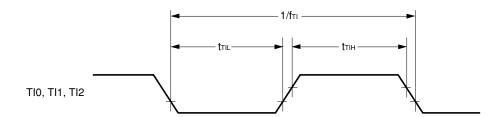


Clock Timing





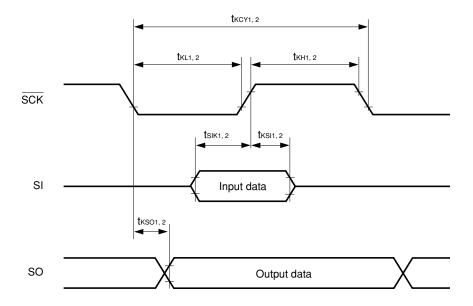
TI0, TI1, TI2 Timing



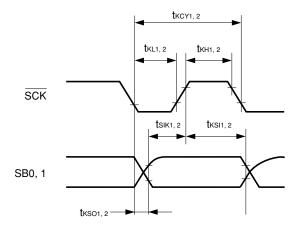


Serial Transfer Timing

3-wire serial I/O mode



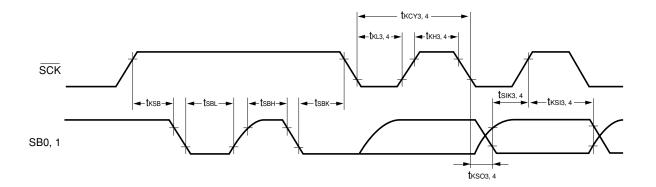
2-wire serial I/O mode



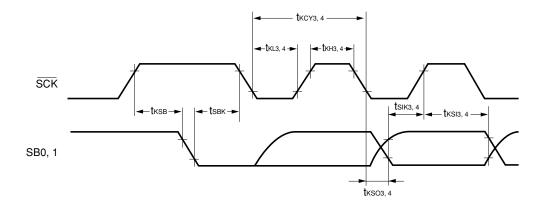


Serial Transfer Timing

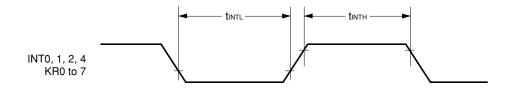
Bus release signal transfer



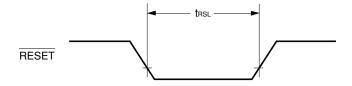
Command signal transfer



Interrupt input timing



RESET input timing





Data Memory Stop Mode Low Supply Voltage Data Retention Characteristics (T_A = -40 to +85°C)

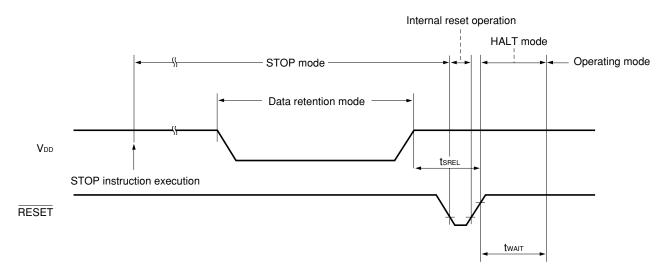
Parameter	Symbol	Test Conditions	MIN.	TYP.	MAX.	Unit
Release signal set time	tsrel		0			μs
Oscillation stabilization	twait	Release by RESET		215/fx		ms
wait time ^{Note 1}		Release by interrupt request		Note 2		ms

- **Notes 1.** The oscillation stabilization wait time is the time during which the CPU operation is stopped to prevent unstable operation at the start of oscillation.
 - 2. Depends on the basic interval timer mode register (BTM) settings (see the table below).

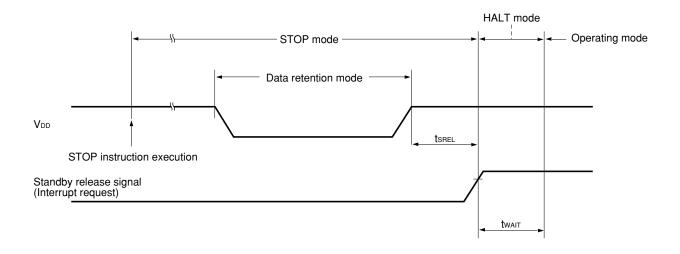
втм3	BTM2	BTM1	ВТМ0	Wait Time		
				fx = 4.19 MHz	fx = 6.0 MHz	
_	0	0	0	2 ²⁰ /fx (approx. 250 ms)	2 ²⁰ /fx (approx. 175 ms)	
_	0	1	1	2 ¹⁷ /fx (approx. 31.3 ms)	2 ¹⁷ /fx (approx. 21.8 ms)	
_	1	0	1	2 ¹⁵ /fx (approx. 7.81 ms)	2 ¹⁵ /fx (approx. 5.46 ms)	
_	1	1	1	2 ¹³ /fx (approx. 1.95 ms)	2 ¹³ /fx (approx. 1.37 ms)	



Data Retention Timing (STOP Mode Release by RESET)



Data Retention Timing (Standby Release Signal: STOP Mode Release by Interrupt Signal)





DC Programming Characteristics (TA = 25 \pm 5°C, VDD = 6.0 \pm 0.25 V, VPP = 12.5 \pm 0.3 V, Vss = 0 V)

Parameter	Symbol	Test Conditions	MIN.	TYP.	MAX.	Unit
Input voltage, high	V _{IH1}	Except X1 and X2 pins	0.7V _{DD}		V _{DD}	V
	V _{IH2}	X1, X2	V _{DD} - 0.5		V _{DD}	V
Input voltage, low	V _{IL1}	Except X1 and X2 pins	0		0.3V _{DD}	V
	V _{IL2}	X1, X2	0		0.4	V
Input leakage current	lu	VIN = VIL OF VIH			10	μΑ
Output voltage, high	Vон	Iон = −1 mA	V _{DD} - 1.0			V
Output voltage, low	Vol	IoL = 1.6 mA			0.4	V
V _{DD} power supply current	IDD				30	mA
VPP power supply current	Ірр	MD0 = VIL, MD1 = VIH			30	mA

Cautions 1. Do not exceed +13.5 V for VPP, including the overshoot.

2. VDD must be applied before VPP, and cut after VPP.

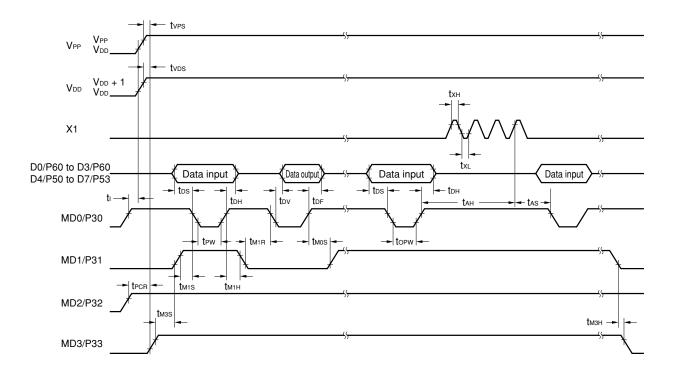
\star AC Programming Characteristics (T_A = 25 ±5°C, V_{DD} = 6.0 ±0.25 V, V_{PP} = 12.5 ±0.3 V, V_{SS} = 0 V)

Parameter	Symbol	Test Conditions	MIN.	TYP.	MAX.	Unit
Address setup time ^{Note} (to MD0↓)	tas		2			μs
MD1 setup time (to MD0↓)	t _{M1} s		2			μs
Data setup time (to MD0↓)	tos		2			μs
Address hold time ^{Note} (from MD0↑)	tан		2			μs
Data hold time (from MD0↑)	tон		2			μs
Data output float delay time from MD0↑	tof		0		130	ns
V _{PP} setup time (to MD3 [↑])	tvps		2			μs
V _{DD} setup time (to MD3↑)	tvos		2			μs
Initial program pulse width	tpw		0.95	1.0	1.05	ms
Additional program pulse width	topw		0.95		21.0	ms
MD0 setup time (to MD1↑)	tмos		2			μs
Data output delay time from MD0↓	tov	MD0 = MD1 = VIL			1	μs
MD1 hold time (from MD0↑)	t м1H	tm1H + tm1R ≥ 50 μs	2			μs
MD1 recovery time (from MD0↓)	t _{M1R}		2			μs
Program counter reset time	tpcr		10			μs
X1 input high-/low-level width	txH, txL		0.125			μs
X1 input frequency	fx				4.19	MHz
Initial mode set time	tı		2			μs
MD3 setup time (to MD1 [↑])	tмзs		2			μs
MD3 hold time (from MD1↓)	tмзн		2			μs
MD3 setup time (to MD0↓)	tмзsr	During program memory read	2			μs
Data output delay time from Address ^{Note}	tdad	During program memory read			2	μs
Data output hold time from Address ^{Note}	thad	During program memory read	0		130	ns
MD3 hold time (from MD0↑)	tмзня	During program memory read	2			μs
Data output float delay time from MD3↓	tofr	During program memory read			2	μs

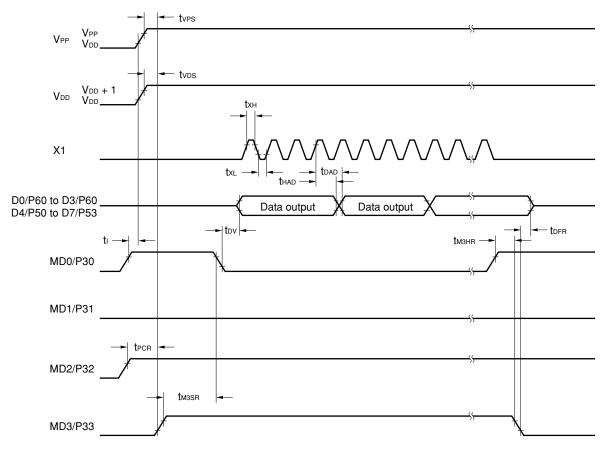
Note The internal address signal is incremented by 1 at the rising edge of the fourth X1 input and is not connected to a pin.



Program Memory Write Timing

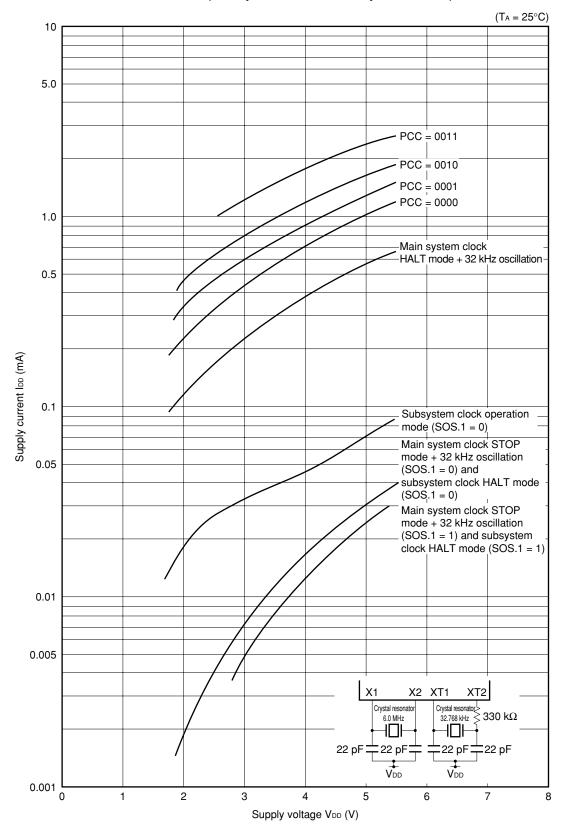


Program Memory Read Timing

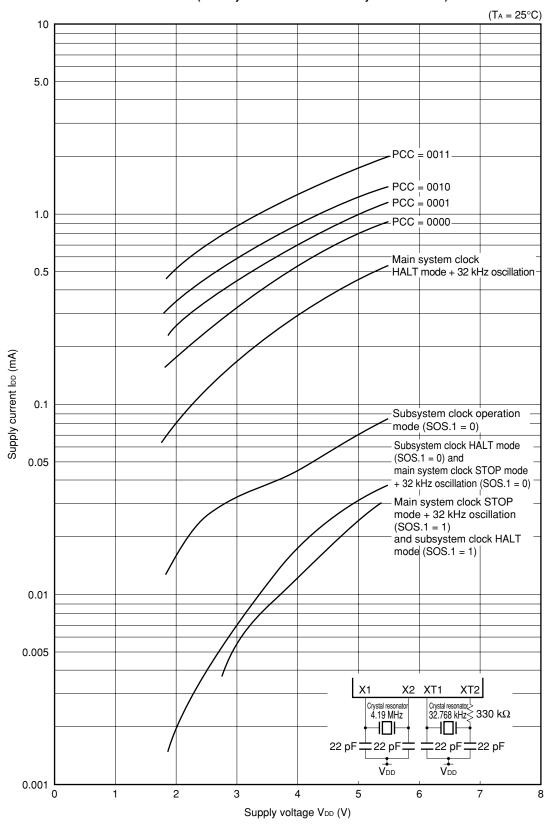


10. CHARACTERISTIC CURVES (REFERENCE VALUES)

IDD VS VDD (Main System Clock: 6.0 MHz Crystal Resonator)

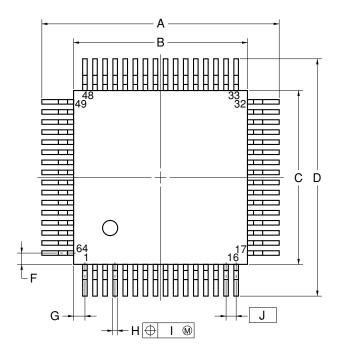


IDD VS VDD (Main System Clock: 4.19 MHz Crystal Resonator)

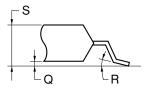


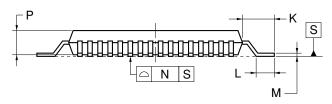
11. PACKAGE DRAWINGS

★ 64-PIN PLASTIC QFP (14x14)



detail of lead end





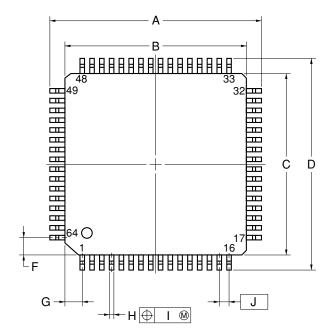
NOTE

Each lead centerline is located within 0.15 mm of its true position (T.P.) at maximum material condition.

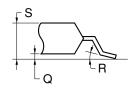
ITEM	MILLIMETERS
Α	17.6±0.4
В	14.0±0.2
С	14.0±0.2
D	17.6±0.4
F	1.0
G	1.0
Н	$0.37^{+0.08}_{-0.07}$
I	0.15
J	0.8 (T.P.)
K	1.8±0.2
L	0.8±0.2
М	0.17 ^{+0.08} _{-0.07}
N	0.10
P	2.55±0.1
Q	0.1±0.1
R	5°±5°
S	2.85 MAX.
	D0100 00 1D0

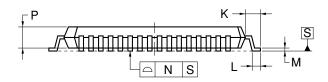
P64GC-80-AB8-5

* 64-PIN PLASTIC LQFP (12x12)



detail of lead end





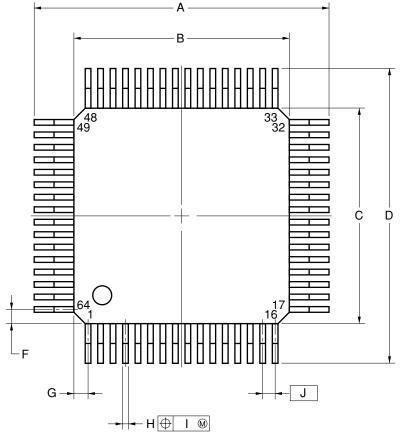
NOTE

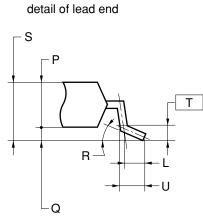
Each lead centerline is located within 0.13 mm of its true position (T.P.) at maximum material condition.

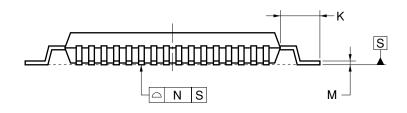
ITEM	MILLIMETERS
Α	14.8±0.4
В	12.0±0.2
С	12.0±0.2
D	14.8±0.4
F	1.125
G	1.125
Н	0.32±0.08
- 1	0.13
J	0.65 (T.P.)
K	1.4±0.2
L	0.6±0.2
М	0.17 ^{+0.08} -0.07
N	0.10
Р	1.4±0.1
Q	0.125±0.075
R	5°±5°
S	1.7 MAX.

P64GK-65-8A8-3

* 64-PIN PLASTIC LQFP (14x14)







NOTE

Each lead centerline is located within 0.20 mm of its true position (T.P.) at maximum material condition.

ITEM	MILLIMETERS
Α	17.2±0.2
В	14.0±0.2
С	14.0±0.2
D	17.2±0.2
F	1.0
G	1.0
Н	0.37 ^{+0.08} -0.07
I	0.20
J	0.8 (T.P.)
K	1.6±0.2
L	0.8
М	0.17 ^{+0.03}
N	0.10
Р	1.4±0.1
Q	0.127±0.075
R	3° +4° -3°
S	1.7 MAX.
T	0.25
U	0.886±0.15
	P64GC-80-8BS



12. RECOMMENDED SOLDERING CONDITIONS

The μ PD75P3116 should be soldered and mounted under the following recommended conditions. For technical information, see the following website.

Semiconductor Device Mount Manual (http://www.necel.com/pkg/en/mount/index.html)

Table 12-1. Surface Mounting Type Soldering Conditions (1/2)

(1) μ PD75P3116GC-AB8: 64-pin plastic QFP (14 \times 14)

Soldering Method	Soldering Conditions	Recommended
		Condition Symbol
Infrared reflow	Package peak temperature: 235°C, Time: 30 seconds max. (at 210°C or higher),	IR35-00-3
	Count: Three times or less	
VPS	Package peak temperature: 215°C, Time: 40 seconds max. (at 200°C or higher),	VP15-00-3
	Count: Three times or less	
Wave soldering	ave soldering Solder bath temperature: 260°C max., Time: 10 seconds max., Count: Once	
Preheating temperature: 120°C max. (package surface temperature)		
Partial heating	Pin temperature: 350°C max., Time: 3 seconds max. (per pin row)	_

Caution Do not use different soldering methods together (except for partial heating).

Remark For soldering methods and conditions other than those recommended above, contact an NEC Electronics sales representative.

(2) μ PD75P3116GK-8A8: 64-pin plastic LQFP (12 × 12)

Soldering Method	Soldering Conditions	Recommended
		Condition Symbol
Infrared reflow	Package peak temperature: 235°C, Time: 30 seconds max. (at 210°C or higher),	IR35-107-2
	Count: Twice or less,	
	Exposure limit: 7 days ^{Note} (after that, prebake at 125°C for 10 to 72 hours)	
VPS	Package peak temperature: 215°C, Time: 40 seconds max. (at 200°C or higher),	VP15-107-2
	Count: Twice or less,	
	Exposure limit: 7 days ^{Note} (after that, prebake at 125°C for 10 to 72 hours)	
Wave soldering	Solder bath temperature: 260°C max., Time: 10 seconds max., Count: Once	WS60-107-1
	Preheating temperature: 120°C max. (package surface temperature)	
	Exposure limit: 7 days ^{Note} (after that, prebake at 125°C for 10 to 72 hours)	
Partial heating	Pin temperature: 350°C max., Time: 3 seconds max. (per pin row)	_

Note After opening the dry pack, store it at 25°C or less and 65% RH or less for the allowable storage period.

Caution Do not use different soldering methods together (except for partial heating).

Remark For soldering methods and conditions other than those recommended above, contact an NEC Electronics sales representative.

Table 12-1. Surface Mounting Type Soldering Conditions (2/2)

(3) μ PD75P3116GC-8BS: 64-pin plastic LQFP (14 \times 14)

Soldering Method	Soldering Conditions	Recommended
		Condition Symbol
Infrared reflow	Package peak temperature: 235°C, Time: 30 seconds max. (at 210°C or higher),	IR35-00-2
	Count: Twice or less	
VPS	Package peak temperature: 215°C, Time: 40 seconds max. (at 200°C or higher),	VP15-00-2
	Count: Twice or less	
Wave soldering	Solder bath temperature: 260°C max., Time: 10 seconds max., Count: Once	WS60-00-1
	Preheating temperature: 120°C max. (package surface temperature)	
Partial heating	Pin temperature: 350°C max., Time: 3 seconds max. (per pin row)	_

Caution Do not use different soldering methods together (except for partial heating).

Remark For soldering methods and conditions other than those recommended above, contact an NEC Electronics sales representative.

\star (4) μ PD75P3116GC-8BS-A: 64-pin plastic LQFP (14 \times 14)

Soldering Method	Soldering Conditions	Recommended
		Condition Symbol
Infrared reflow	Package peak temperature: 260°C, Time: 60 seconds max. (at 220°C or higher),	IR60-207-3
	Count: Three times or less,	
	Exposure limit: 7 days ^{Note} (after that, prebake at 125°C for 20 to 72 hours)	
Wave soldering	For details, contact an NEC Electronics sales representative.	_
Partial heating	Pin temperature: 350°C max., Time: 3 seconds max. (per pin row)	_

Note After opening the dry pack, store it at 25°C or less and 65% RH or less for the allowable storage period.

Caution Do not use different soldering methods together (except for partial heating).

- Remarks 1. Products with "-A" at the end of the part number are lead-free products.
 - **2.** For soldering methods and conditions other than those recommended above, contact an NEC Electronics sales representative.

Table 12-1. Surface Mounting Type Soldering Conditions (2/2)

\star (3) μ PD75P3116GC-8BS: 64-pin plastic LQFP (14 \times 14)

Soldering Method	Soldering Conditions	Recommended Condition Symbol
Infrared reflow	Package peak temperature: 235°C, Time: 30 seconds max. (at 210°C or higher), Count: Twice or less	IR35-00-2
VPS	Package peak temperature: 215°C, Time: 40 seconds max. (at 200°C or higher), Count: Twice or less	VP15-00-2
Wave soldering	Solder bath temperature: 260°C max., Time: 10 seconds max., Count: Once, Preheating temperature: 120°C max. (package surface temperature)	WS60-00-1
Partial heating	Pin temperature: 300°C max., Time: 3 seconds max. (per pin row)	_

Caution Do not use different soldering methods together (except for partial heating).



APPENDIX A. LIST OF μ PD75308B, 753108, AND 75P3116 FUNCTIONS

	Paramotor	UDD75200D	,,DD752109	UDD75D2116
Parameter		μPD75308B	μPD753108	μPD75P3116
Program memory		Mask ROM 0000H to 1F7FH (8064 × 8 bits)	Mask ROM 0000H to 1FFFH (8192 × 8 bits)	One-time PROM 0000H to 3FFFH (16384 × 8 bits)
Data memory			000H to 1FFH (512 × 4 bits)	
CPU		75X Standard 75XL CPU		
Instruction execution	When main system clock is selected	0.95, 1.91, 15.3 μ s (during 4.19 MHz operation)	• 0.95, 1.91, 3.81, 15.3 μs (during 4.19 MHz operatio • 0.67, 1.33, 2.67, 10.7 μs (during 6.0 MHz operation	
time	When subsystem clock is selected	122 μs (during 32.768 kHz o	peration)	
Stack	SBS register	None	SBS.3 = 1: Mk I mode selection SBS.3 = 0: Mk II mode selection	
	Stack area	000H to 0FFH	000H to 1FFH	
	Subroutine call instruction stack operation	2-byte stack	When Mk I mode: 2-byte s When Mk II mode: 3-byte s	
Instruction BRA laddr1 CALLA laddr1		Unavailable	When Mk I mode: Unavailable When Mk II mode: Available	
	MOVT XA, @BCDE MOVT XA, @BCXA BR BCDE BR BCXA		Available	
	CALL laddr	3 machine cycles	Mk I mode: 3 machine cyc Mk II mode: 4 machine cyc	
	CALLF !faddr	2 machine cycles	Mk I mode: 2 machine cycles Mk II mode: 3 machine cycles	
I/O ports	CMOS input	8	8	
	CMOS I/O	16	20	
	Bit port output	8	0	
	N-ch open-drain I/O	8	4	
	Total	40	32	
LCD controller/driver		Segment selection: 24/28/32 (can be changed to CMOS I/O port in 4-bit units; max. 8)	Segment selection: 16/20/24 segments (can be changed to CMOS I/O port in 4-bit units; max.	
		Display mode selection: Static, 1/2 duty (1/2 bias), 1/3 duty (1/2 bias), 1 (1/3 bias), 1/4 duty (1/3 bias)		ty (1/2 bias), 1/3 duty
				No on-chip split resistor for LCD driver
Timer		3 channels • Basic interval timer: 1 channel • 8-bit timer/event counter: 1 channel • Watch timer: 1 channel	5 channels Basic interval timer/watche Betit timer/event counter: (can be used as 16-bit time) Watch timer: 1 channel	3 channels



F	Parameter	μPD75308B	μPD753108	μPD75P3116	
Clock output (PCL)		Φ, 524, 262, 65.5 kHz (Main system clock: during 4.19 MHz operation)	 Φ, 524, 262, 65.5 kHz (Main system clock: during 4.19 MHz operation) Φ, 750, 375, 93.8 kHz (Main system clock: during 6.0 MHz operation) 		
BUZ output (BUZ)		2 kHz (Main system clock: during 4.19 MHz operation)	2, 4, 32 kHz (Main system clock: during 4.19 MHz operation or subsystem clock: during 32.768 kHz operation) 2.93, 5.86, 46.9 kHz (Main system clock: during 6.0 MHz operation)		
Serial interface		3 modes are available • 3-wire serial I/O mode ··· MSB/LSB can be selected for transfer first bit • 2-wire serial I/O mode • SBI mode		ransfer first bit	
SOS register Feedback resistor cut flag (SOS.0)		None	Contained		
	Sub-oscillator current cut flag (SOS.1)	None	Contained		
Register bank selection register (RBS)		None	Yes		
Standby release	e by INT0	No	Yes		
Vectored interru	upts	External: 3, Internal: 3	External: 3, Internal: 5		
Supply voltage		V _{DD} = 2.0 to 6.0 V	V _{DD} = 1.8 to 5.5 V		
Operating ambi	ent temperature	T _A = -40 to +85°C		_	
Package		80-pin plastic QFP (14 × 20) 80-pin plastic QFP (14 × 14) 80-pin plastic TQFP (Fine pitch) (12 × 12)	• 64-pin plastic QFP (14 × 14) • 64-pin plastic LQFP (12 × 12) • 64-pin plastic TQFP (12 × 12) • 64-pin plastic LQFP (14 × 14)	• 64-pin plastic QFP (14 × 14) • 64-pin plastic LQFP (12 × 12) • 64-pin plastic LQFP (14 × 14)	



APPENDIX B. DEVELOPMENT TOOLS

The following development tools have been provided for system development using the μ PD75P3116. In the 75XL Series, a common relocatable assembler is used in combination with a device file dedicated to each model.

*	RA75X relocatable assembler	Host Machine		Part Number	
			OS	Supply Medium	(Product Name)
		PC-9800 Series	MS-DOS™	3.5" 2HD	μS5A13RA75X
			(Ver.3.30 to Ver.6.2 ^{Note})		
		IBM PC/AT™ or compatibles	Refer to OS for IBM PCs	3.5" 2HC	μS7B13RA75X

*	Device file	Host Machine			Part Number
			OS	Supply Medium	(Product Name)
		PC-9800 Series	MS-DOS	3.5" 2HD	μS5A13DF753108
			(Ver.3.30 to Ver.6.2 ^{Note})		
		IBM PC/AT or compatibles	Refer to OS for IBM PCs	3.5" 2HC	μS7B13DF753108

Note Ver. 5.00 and later include a task swapping function, but this function cannot be used in this software.

Remark Operation of the assembler and device file is guaranteed only when using the host machine and OS described above.



PROM Write Tools

	Hardware	PG-1500	This is a PROM writer that can program a single-chip microcontroller with PROM in stand-alone mode or under the control of a host machine when connected with the supplied accessory board and optional programmer adapter. It can also program typical PROMs in capacities ranging from 256 Kb to 4 Mb.			
*		PA-75P3116GC	This is a PROM programmer adapter for the μ PD75P3116GC-AB8. It can be used when connected to the PG-1500.			
*		PA-75P3116GK	This is a PROM programmer adapter for the μ PD75P3116GK-8A8. It can be used when connected to the PG-1500.			
*		PA-75P3116GC-8BS	This is a PROM programmer adapter for the μ PD75P3116GC-8BS. It can be used when connected to the PG-1500.			
	Software	PG-1500 controller	Connects the PG-1500 to the host machine via serial and parallel interfaces and controls the PG-1500 on the host machine.			
			Host machine			Part number
				OS	Supply medium	(Product name)
			PC-9800 Series	MS-DOS	3.5" 2HD	μS5A13PG1500
				(Ver.3.30 to Ver.6.2 ^{Note})		
			IBM PC/AT or compatible	Refer to OS for IBM PCs	3.5" 2HD	μS7B13PG1500

Note Ver. 5.00 and later include a task swapping function, but this function cannot be used in this software.

Remark Operation of the PG-1500 controller is guaranteed only when using the host machine and OS described above.

Debugging Tools

An in-circuit emulator (IE-75001-R) is provided as a program debugging tool for the μ PD75P3116.

The system configuration using this in-circuit emulator is shown below.

Hardware IE-75001-R The IE-75001-R is an in-circuit emulator to be used for hardware and software debugging during development of application systems using the 75X or 75XL Series products. The IE-75001-R is used in combination with an emulation board (IE-75300-R-EM) and emulation probe (EP-753108GC-R or EP-753108GK-R) (both sold separately). Highly efficient debugging can be performed when connected to the host machine and PROM programmer. IE-75300-R-EM This is an emulation board for evaluating application systems using the μ PD75P3116. It is used in combination with the IE-75001-R. EP-753108GC-R This is an emulation probe for the μ PD75P3116GC. When being used, it is connected with the IE-75001-R and the IE-75300-R-EM. It includes a 64-pin conversion socket (EV-9200GC-64) to facilitate connection with the target EV-9200GC-64 system. EP-753108GK-R This is an emulation probe for the μ PD75P3116GK. When being used, it is connected with the IE-75001-R and the IE-75300-R-EM. TGK-064SBW It includes a 64-pin conversion adapter (TGK-064SBW) to facilitate connection with the target Note 1 system. Software IE control program This program can control the IE-75001-R on a host machine when connected to the IE-75001-R via an RS-232C or Centronics interface. Host machine Part number (Product name) os Supply medium PC-9800 Series MS-DOS 3.5" 2HD μS5A13IE75X Ver.3.30 to Ver.6.2Note 2 IBM PC/AT 3.5" 2HC Refer to OS for μS7B13IE75X **IBM PCs** or compatible

★ Notes 1. This is a product of TOKYO ELETECH CORPORATION.

Contact: Daimaru Kogyo, Ltd. Tokyo Electronic Department (TEL: +81-3-3820-7112)

Osaka Electronic Department (TEL: +81-6-6244-6672)

2. Ver. 5.00 and later include a task swapping function, but this function cannot be used in this software.

Remarks 1. Operation of the IE control program is guaranteed only when using the host machine and OS described above.

2. The μ PD753104, 753106, 753108, and 75P3116 are generically called the μ PD753108 Subseries.



OS for IBM PCs

The following operating systems for IBM PCs are supported.

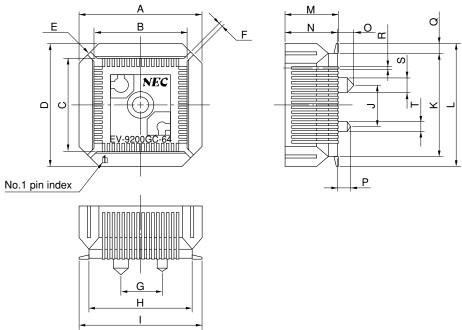
os	Version
PC DOS™	Ver.3.1 to 6.3 J6.1/V ^{Note} to J6.3/V ^{Note}
MS-DOS	Ver.5.0 to 6.2 5.0/V ^{Note} to 6.2/V ^{Note}
IBM DOS™	J5.02/V ^{Note}

Note Only English mode is supported.

Caution Ver. 5.0 and later include a task swapping function, but this function cannot be used in this software.

★ Package Drawing and Recommended Footprint of Conversion Socket (EV-9200GC-64)

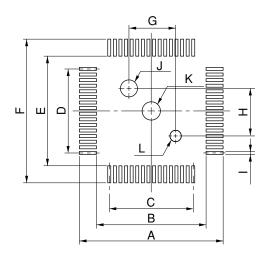
Figure B-1. EV-9200GC-64 Package Drawing (For Reference Only)



EV-9200GC-64-G0E

ITEM	MILLIMETERS	INCHES
Α	18.8	0.74
В	14.1	0.555
С	14.1	0.555
D	18.8	0.74
E	4-C 3.0	4-C 0.118
F	0.8	0.031
G	6.0	0.236
Н	15.8	0.622
ı	18.5	0.728
J	6.0	0.236
K	15.8	0.622
L	18.5	0.728
М	8.0	0.315
N	7.8	0.307
0	2.5	0.098
Р	2.0	0.079
Q	1.35	0.053
R	0.35±0.1	$0.014^{+0.004}_{-0.005}$
S	φ2.3	Ø0.091
Т	φ1.5	φ0.059

Figure B-2. EV-9200GC-64 Recommended Footprint (For Reference Only)



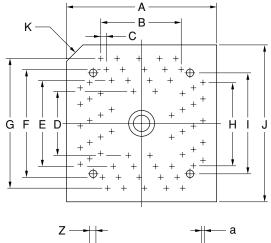
EV-9200GC-64-P1E

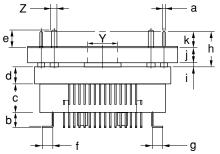
ITEM	MILLIMETERS	INCHES
Α	19.5	0.768
В	14.8	0.583
С	$0.8\pm0.02 \times 15=12.0\pm0.05$	$0.031^{+0.002}_{-0.001} \times 0.591 = 0.472^{+0.003}_{-0.002}$
D	$0.8\pm0.02 \times 15=12.0\pm0.05$	$0.031^{+0.002}_{-0.001} \times 0.591 = 0.472^{+0.003}_{-0.002}$
Е	14.8	0.583
F	19.5	0.768
G	6.00±0.08	$0.236^{+0.004}_{-0.003}$
Н	6.00±0.08	$0.236^{+0.004}_{-0.003}$
- 1	0.5±0.02	$0.197^{+0.001}_{-0.002}$
J	φ2.36±0.03	ϕ 0.093 $^{+0.001}_{-0.002}$
K	φ2.2±0.1	ϕ 0.087 $^{+0.004}_{-0.005}$
L	φ1.57±0.03	ϕ 0.062 $^{+0.001}_{-0.002}$

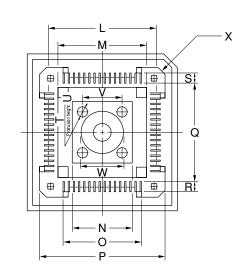
Caution Dimensions of mount pad for EV-9200 and that for target device (QFP) may be different in some parts. For the recommended mount pad dimensions for QFP, refer to "SEMICONDUCTOR DEVICE MOUNTING TECHNOLOGY MANUAL" (C10535E).

★ Package Drawing of Conversion Adapter (TGK-064SBW)

Figure B-3. TGK-064SBW Package Drawing (For Reference Only)







ITEM	MILLIMETERS	INCHES
Α	18.4	0.724
В	0.65x15=9.75	0.026x0.591=0.384
С	0.65	0.026
D	7.75	0.305
Е	10.15	0.400
F	12.55	0.494
G	14.95	0.589
Н	0.65x15=9.75	0.026x0.591=0.384
I	11.85	0.467
J	18.4	0.724
K	C 2.0	C 0.079
L	12.45	0.490
M	10.25	0.404
N	7.7	0.303
0	10.02	0.394
Р	14.92	0.587
Q	11.1	0.437
R	1.45	0.057
S	1.45	0.057
Т	4- <i>\phi</i> 1.3	4-φ0.051
U	1.8	0.071
V	5.0	0.197
W	φ5.3	φ0.209
Х	4-C 1.0	4-C 0.039

 ϕ 3.55

φ0.140 φ0.035

_	ITEM	MILLIMETERS	INCHES
-	a	φ0.3	φ0.012
_	b	1.85	0.073
-	С	3.5	0.138
_	d	2.0	0.079
_	e	3.9	0.154
_	f	1.325	0.052
	g	1.325	0.052
	h	5.9	0.232
	i	0.8	0.031
	j	2.4	0.094
	k	2.7	0.106
			TOV 0646BW C1E

TGK-064SBW-G1E



★ Notes on Target System Design

The following shows a diagram of the connection conditions between the emulation probe, conversion connector and conversion socket or conversion adapter.

Design your system making allowances for conditions such as the form of parts mounted on the target system, as shown below.

Table B-1. Distance Between In-Circuit Emulator and Conversion Socket

Emulation Probe	Conversion Socket/ Conversion Adapter	Distance Between In-Circuit Emulator and Conversion Socket or Conversion Adapter
EP-753108GC-R	EV-9200GC-64	700 mm
EP-753108GK-R	TGK-064SBW	700 mm

Figure B-4. Distance Between In-Circuit Emulator and Conversion Socket or Conversion Adapter (1)

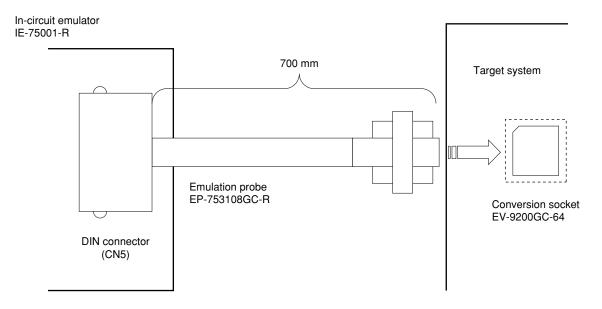
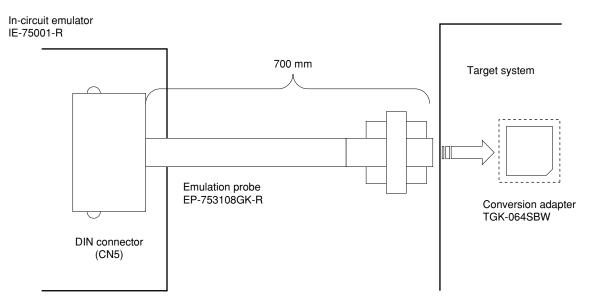


Figure B-5. Distance Between In-Circuit Emulator and Conversion Socket or Conversion Adapter (2)



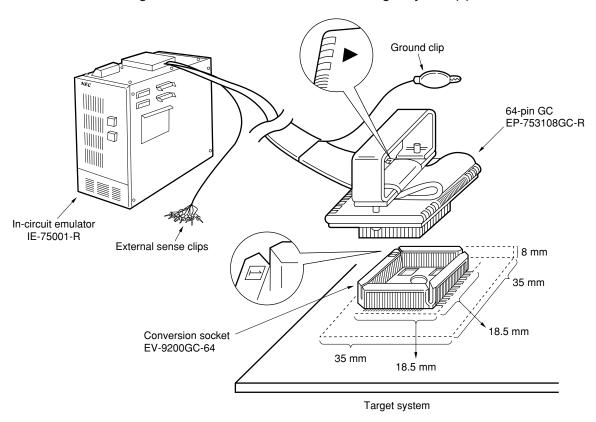
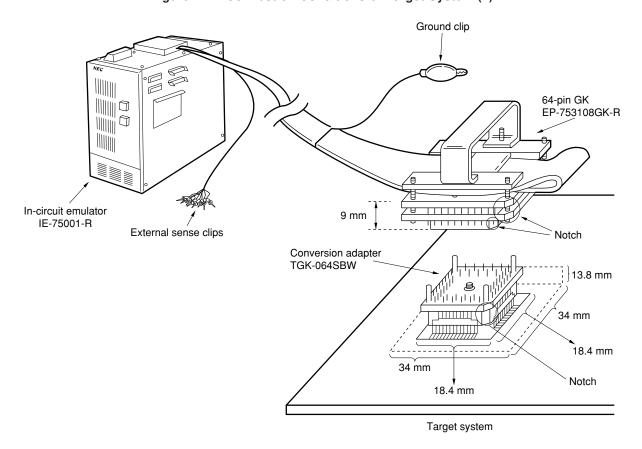


Figure B-6. Connection Conditions of Target System (1)

Figure B-7. Connection Conditions of Target System (2)





* APPENDIX C. RELATED DOCUMENTS

The related documents indicated in this publication may include preliminary versions. However, preliminary versions are not marked as such.

Documents Related to Devices

Document Name	Document No.
μPD753104, 753106, 753108 Data Sheet	U10086E
μPD75P3116 Data Sheet	This document
μPD753108 User's Manual	U10890E
75XL Series Selection Guide	U10453E

Documents Related to Development Tools (Software) (User's Manuals)

Document Name		Document No.
RA75X Assembler Package	Operation	U12622E
	Language	U12385E
	Structured Assembler Preprocessor	U12598E

Documents Related to Development Tools (Hardware) (User's Manuals)

Document Name	Document No.
IE-75000-R, IE-75001-R In-Circuit Emulator	EEU-1455
IE-75300-R-EM Emulation Board	U11354E
EP-753108GC-R, EP-753108GK-R Emulation Probe	EEU-1495

Documents Related to PROM Writing (User's Manuals)

Document Name		Document No.
PG-1500 PROM Programmer		U11940E
PG-1500 Controller	PC-9800 Series (MS-DOS) Based	EEU-1291
	IBM PC Series (PC DOS) Based	U10540E

Caution The related documents listed above are subject to change without notice. Be sure to use the latest version of each document for designing.



Other Related Documents

Document Name	Document No.
SEMICONDUCTOR SELECTION GUIDE - Products & Packages -	X13769E
Semiconductor Device Mounting Technology Manual	C10535E
Quality Grades on NEC Semiconductor Devices	C11531E
NEC Semiconductor Device Reliability/Quality Control System	C10983E
Guide to Prevent Damage for Semiconductor Devices by Electrostatic Discharge (ESD)	C11892E

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NOTES FOR CMOS DEVICES -

1) VOLTAGE APPLICATION WAVEFORM AT INPUT PIN

Waveform distortion due to input noise or a reflected wave may cause malfunction. If the input of the CMOS device stays in the area between $V_{\rm IL}$ (MAX) and $V_{\rm IH}$ (MIN) due to noise, etc., the device may malfunction. Take care to prevent chattering noise from entering the device when the input level is fixed, and also in the transition period when the input level passes through the area between $V_{\rm IL}$ (MAX) and $V_{\rm IH}$ (MIN).

(2) HANDLING OF UNUSED INPUT PINS

Unconnected CMOS device inputs can be cause of malfunction. If an input pin is unconnected, it is possible that an internal input level may be generated due to noise, etc., causing malfunction. CMOS devices behave differently than Bipolar or NMOS devices. Input levels of CMOS devices must be fixed high or low by using pull-up or pull-down circuitry. Each unused pin should be connected to VDD or GND via a resistor if there is a possibility that it will be an output pin. All handling related to unused pins must be judged separately for each device and according to related specifications governing the device.

③ PRECAUTION AGAINST ESD

A strong electric field, when exposed to a MOS device, can cause destruction of the gate oxide and ultimately degrade the device operation. Steps must be taken to stop generation of static electricity as much as possible, and quickly dissipate it when it has occurred. Environmental control must be adequate. When it is dry, a humidifier should be used. It is recommended to avoid using insulators that easily build up static electricity. Semiconductor devices must be stored and transported in an anti-static container, static shielding bag or conductive material. All test and measurement tools including work benches and floors should be grounded. The operator should be grounded using a wrist strap. Semiconductor devices must not be touched with bare hands. Similar precautions need to be taken for PW boards with mounted semiconductor devices.

(4) STATUS BEFORE INITIALIZATION

Power-on does not necessarily define the initial status of a MOS device. Immediately after the power source is turned ON, devices with reset functions have not yet been initialized. Hence, power-on does not guarantee output pin levels, I/O settings or contents of registers. A device is not initialized until the reset signal is received. A reset operation must be executed immediately after power-on for devices with reset functions.

(5) POWER ON/OFF SEQUENCE

In the case of a device that uses different power supplies for the internal operation and external interface, as a rule, switch on the external power supply after switching on the internal power supply. When switching the power supply off, as a rule, switch off the external power supply and then the internal power supply. Use of the reverse power on/off sequences may result in the application of an overvoltage to the internal elements of the device, causing malfunction and degradation of internal elements due to the passage of an abnormal current.

The correct power on/off sequence must be judged separately for each device and according to related specifications governing the device.

6 INPUT OF SIGNAL DURING POWER OFF STATE

Do not input signals or an I/O pull-up power supply while the device is not powered. The current injection that results from input of such a signal or I/O pull-up power supply may cause malfunction and the abnormal current that passes in the device at this time may cause degradation of internal elements. Input of signals during the power off state must be judged separately for each device and according to related specifications governing the device.

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- Availability of related technical literature
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- Network requirements

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